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**Yamane et al.**

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(54) **METHOD FOR MANUFACTURING LIGHT EMITTING DEVICE, AND LIGHT EMITTING DEVICE**

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(\*) Notice: This patent is subject to a terminal disclaimer.

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(22) Filed: **May 6, 2020**

**Related U.S. Patent Documents**

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Filed: **Oct. 9, 2013**

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(63) Continuation of application No. 15/860,927, filed on Jan. 3, 2018, now Pat. No. Re. 48,033, which is an  
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**H01L 51/52** (2006.01)  
**H01L 51/56** (2006.01)

(52) **U.S. Cl.**  
CPC ..... **H01L 33/36** (2013.01); **H01L 51/56** (2013.01); **H01L 51/5253** (2013.01); **H01L 2251/566** (2013.01)

(58) **Field of Classification Search**

CPC ..... H01L 33/36; H01L 51/5253; H01L 51/56;  
H01L 2251/566; H01L 33/54; H01L  
21/3043

See application file for complete search history.

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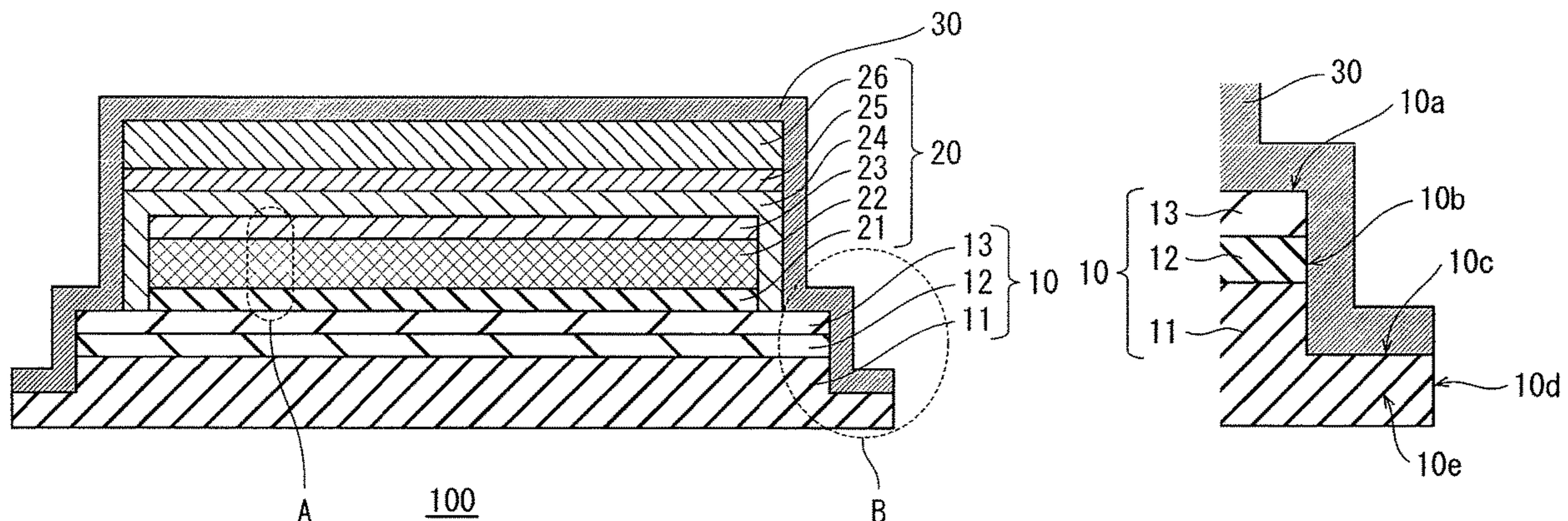
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(57) **ABSTRACT**

A method for manufacturing a light-emitting device, comprising: forming, over a substrate, a plurality of multilayered light-emitting structures each including a first electrode, a light-emitting layer, and a second electrode; forming, in the substrate, a plurality of grooves that surround the multilayered light-emitting structures individually; forming, over the substrate, a sealing film that covers the multilayered light-emitting structures and the grooves; and separating the multilayered light-emitting structures from one another after forming the sealing film, by cutting the substrate such that, in each groove, part of the sealing film covering a given inner side surface of the groove remains, the given inner side

(Continued)



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surface being adjacent to any of the multilayered light-emitting structures.

## 4 Claims, 12 Drawing Sheets

### Related U.S. Application Data

application for the reissue of Pat. No. 9,231,156, which is a continuation of application No. PCT/JP2012/005604.

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FIG. 1A

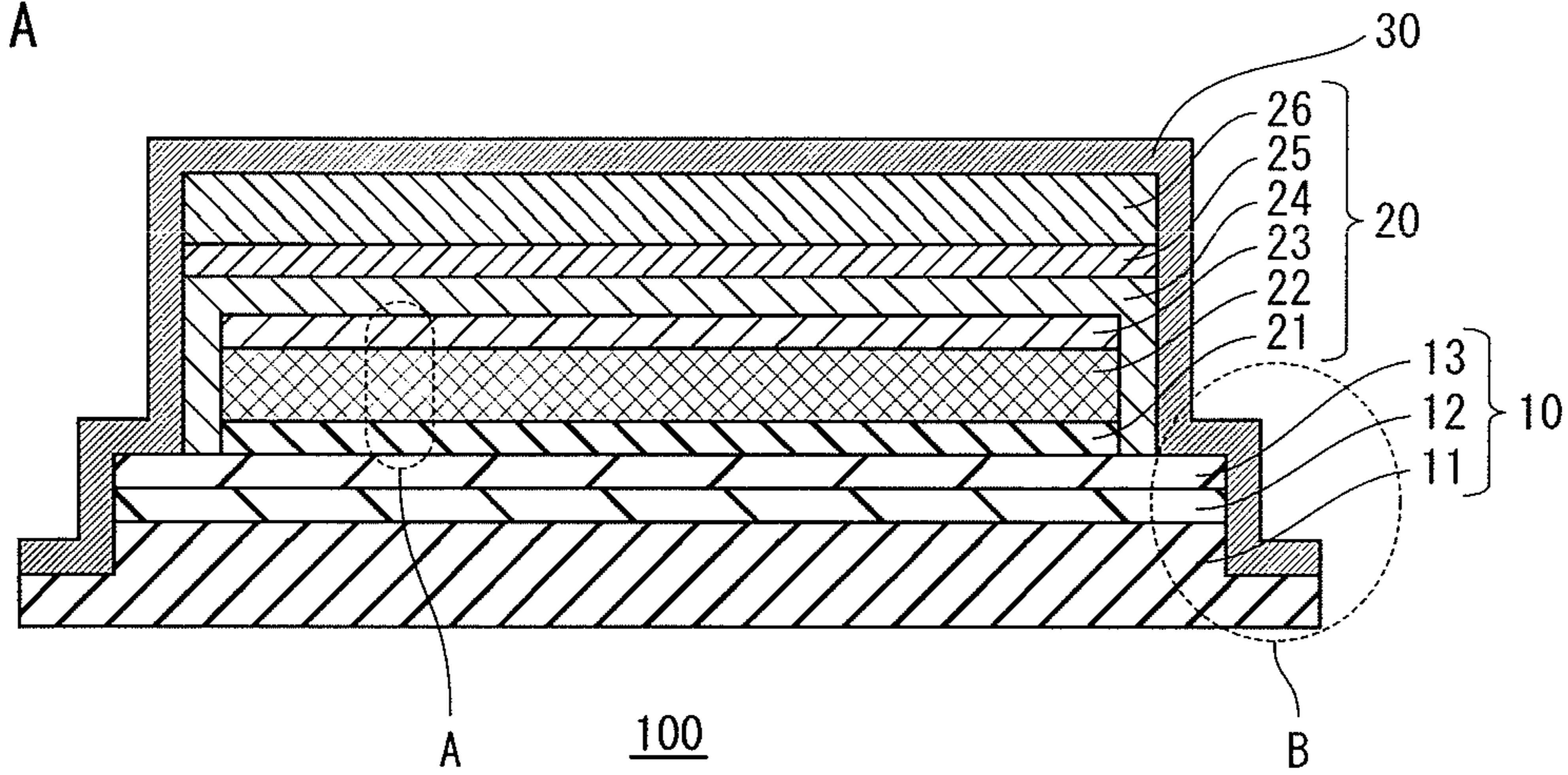


FIG. 1B

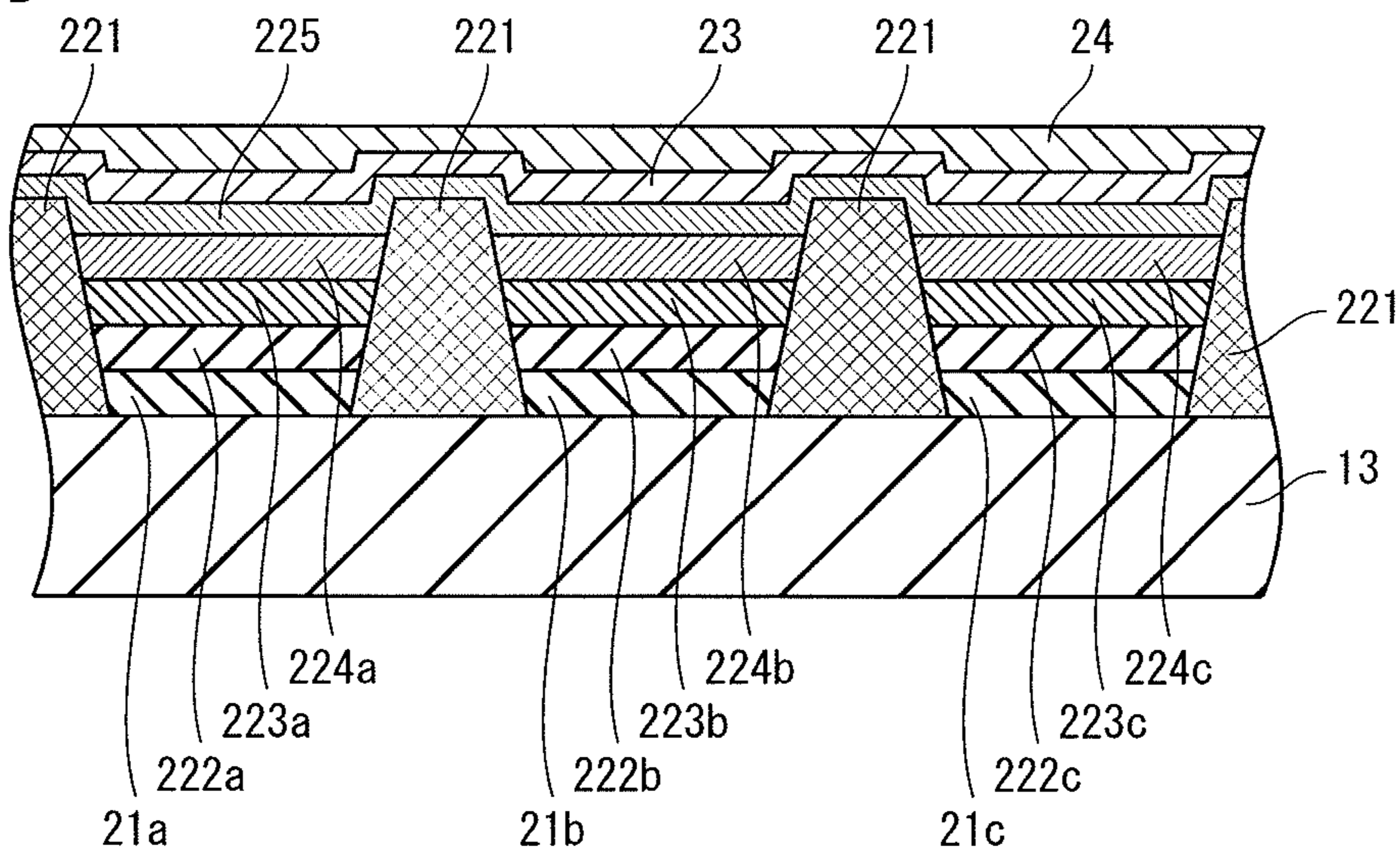


FIG. 1C

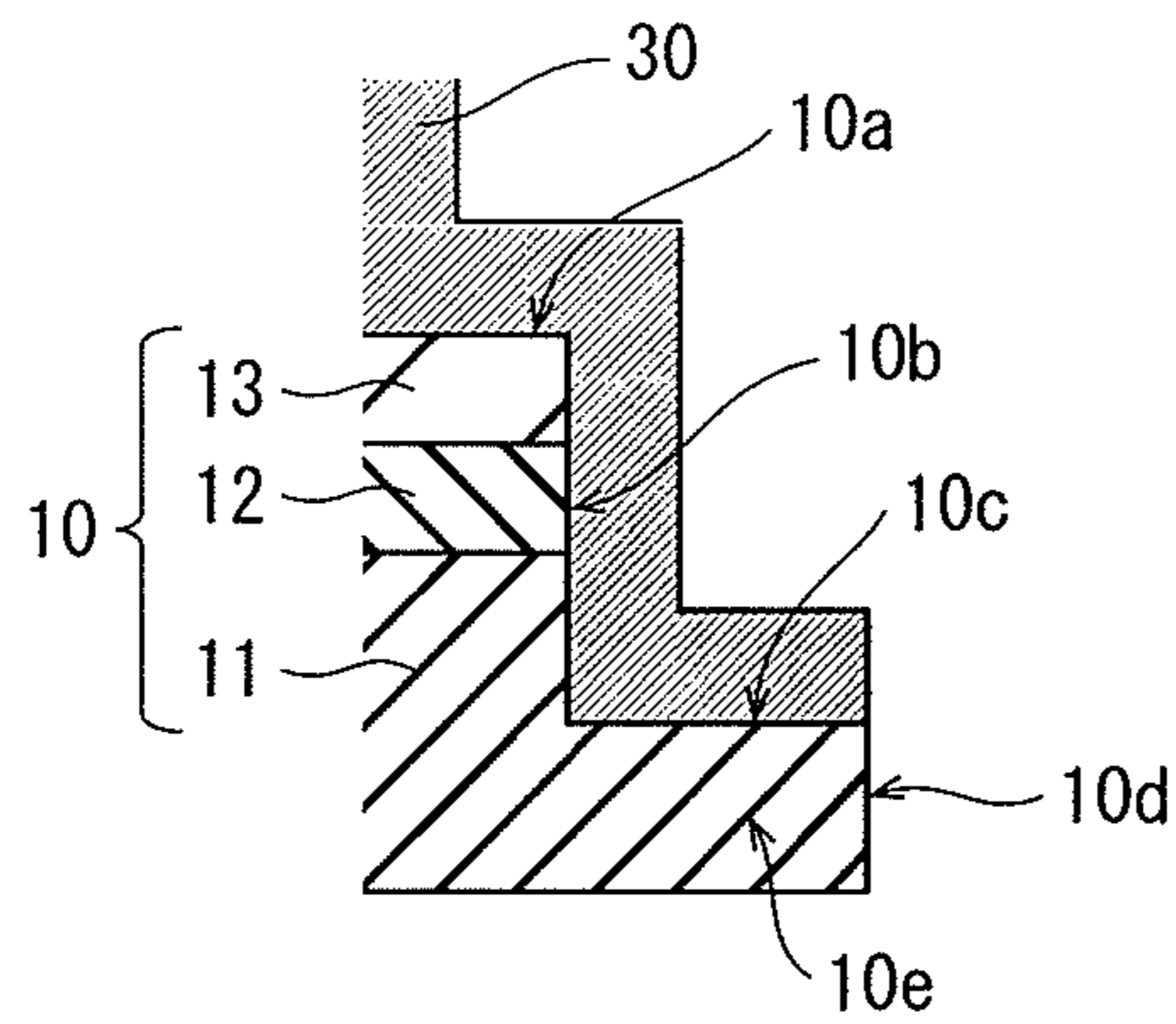


FIG. 2A

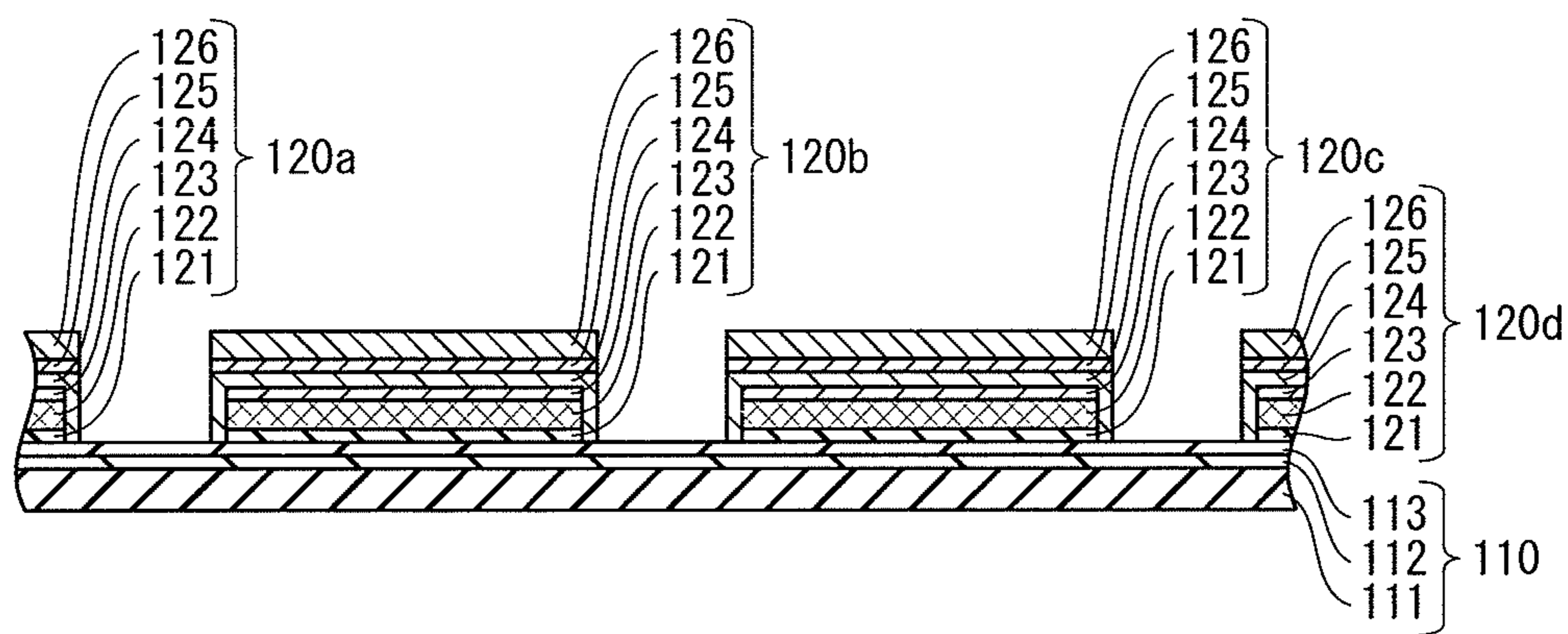


FIG. 2B

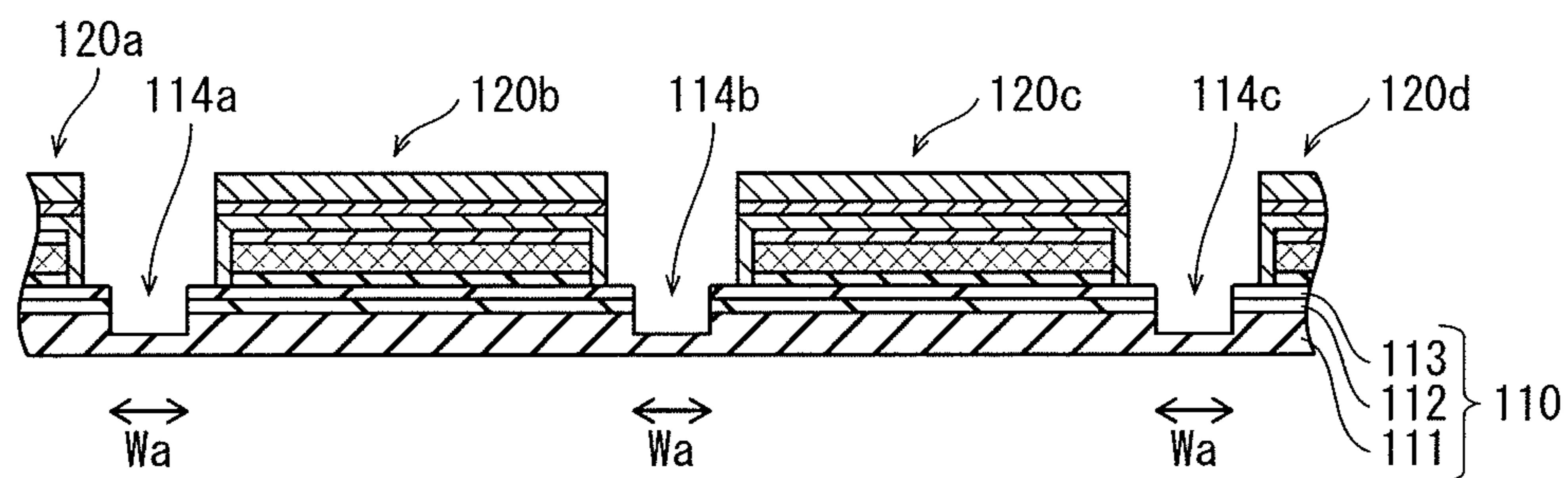


FIG. 3

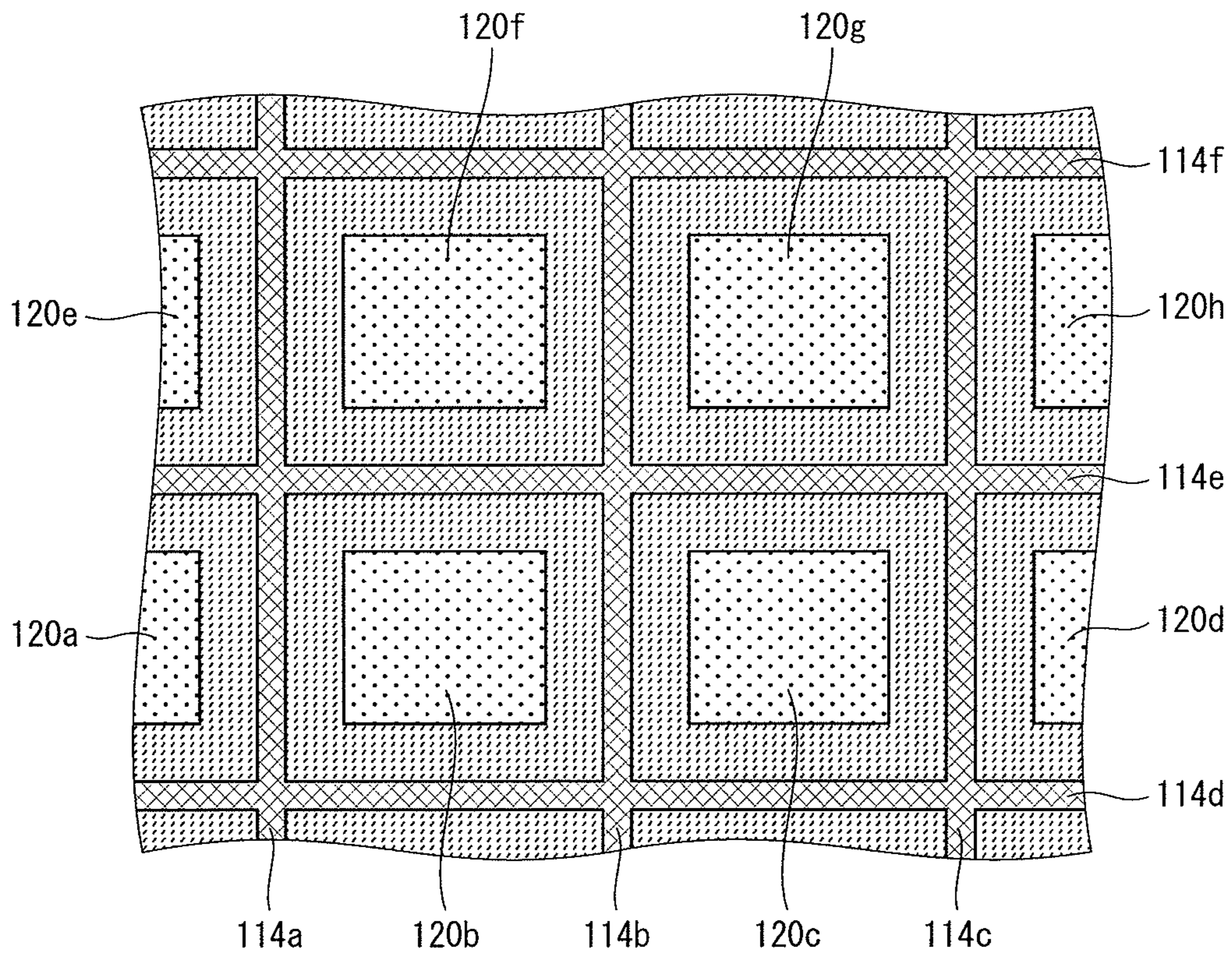




FIG. 4A

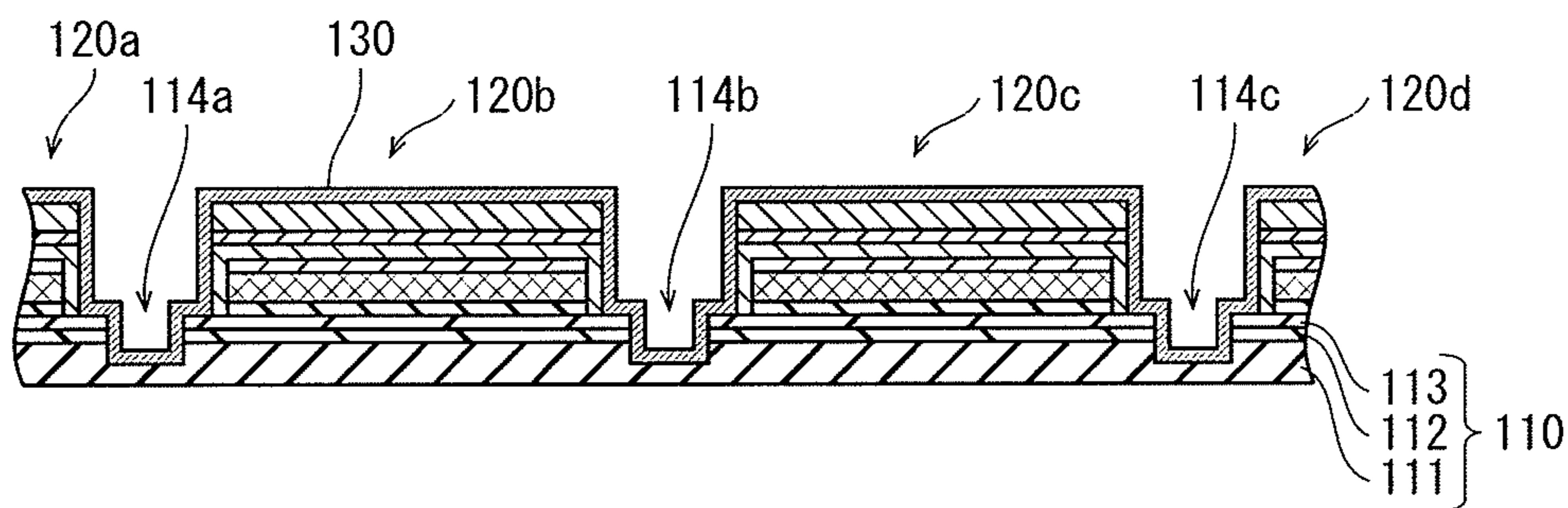


FIG. 4B

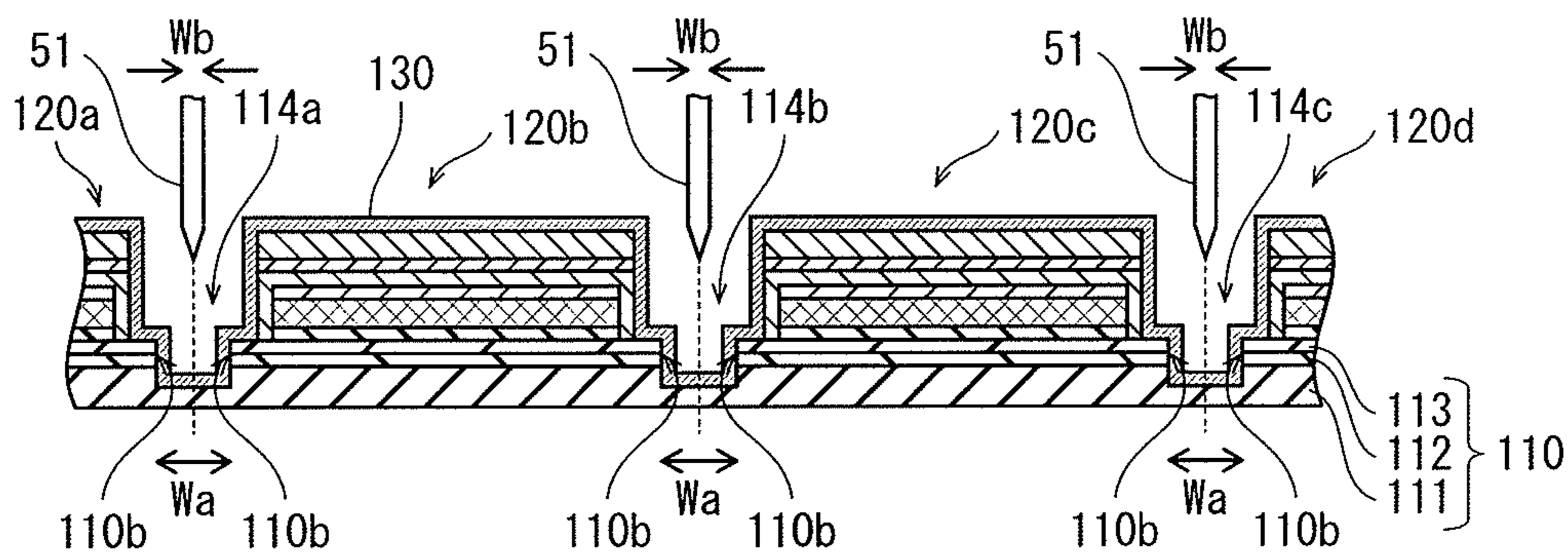


FIG. 4C

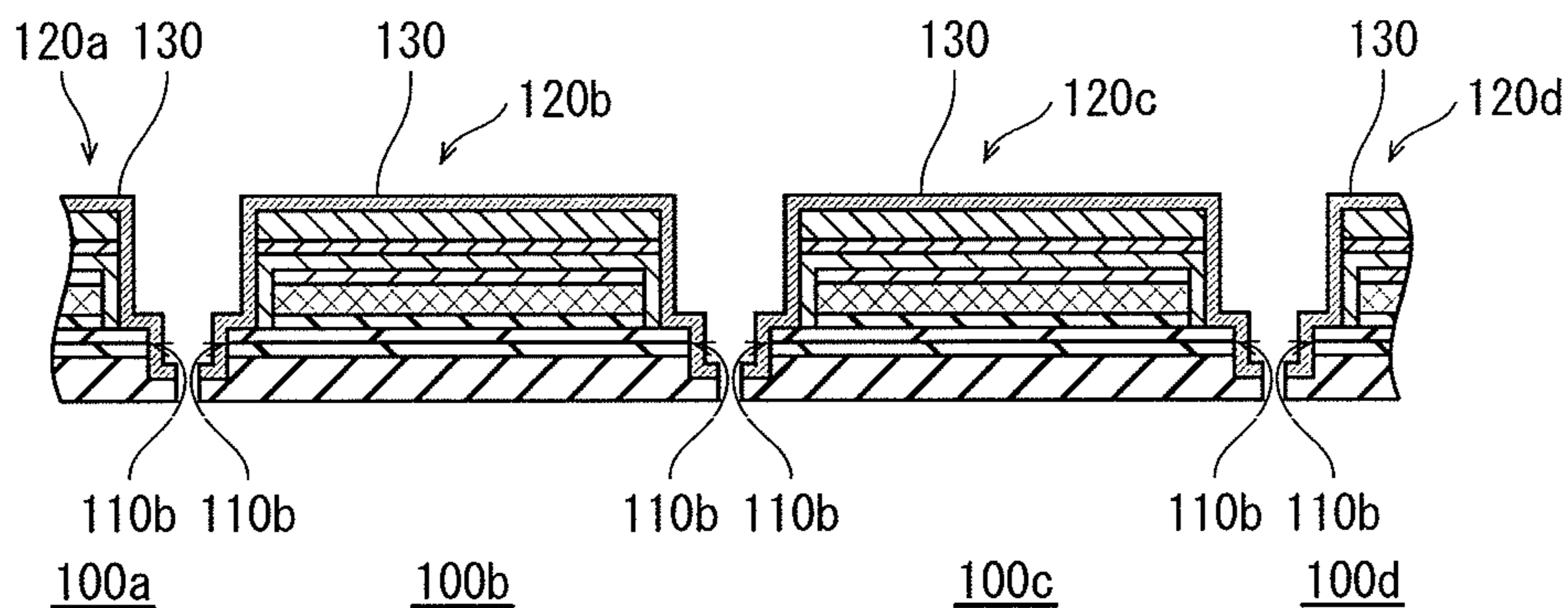


FIG. 5A

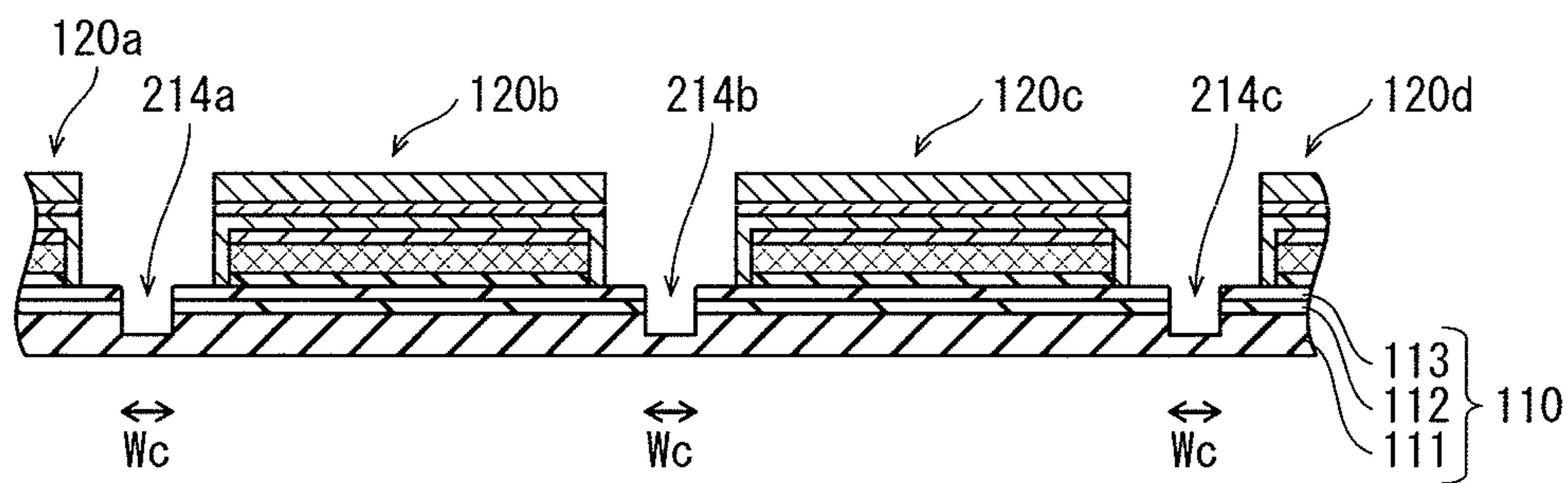


FIG. 5B

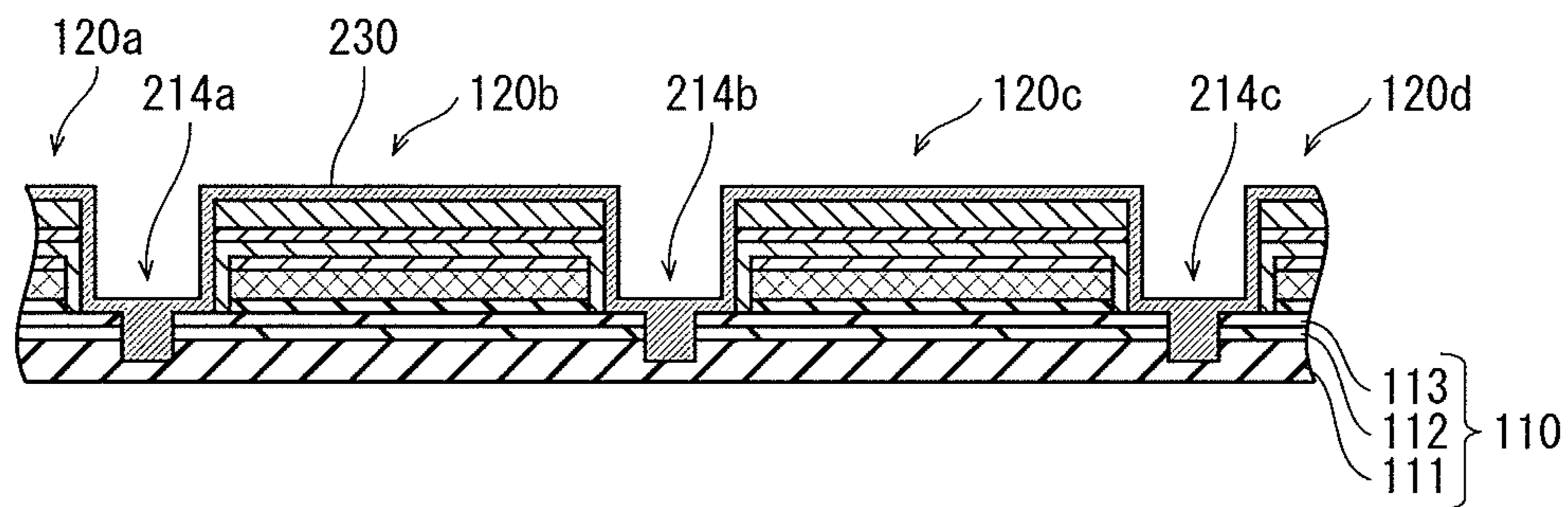


FIG. 5C

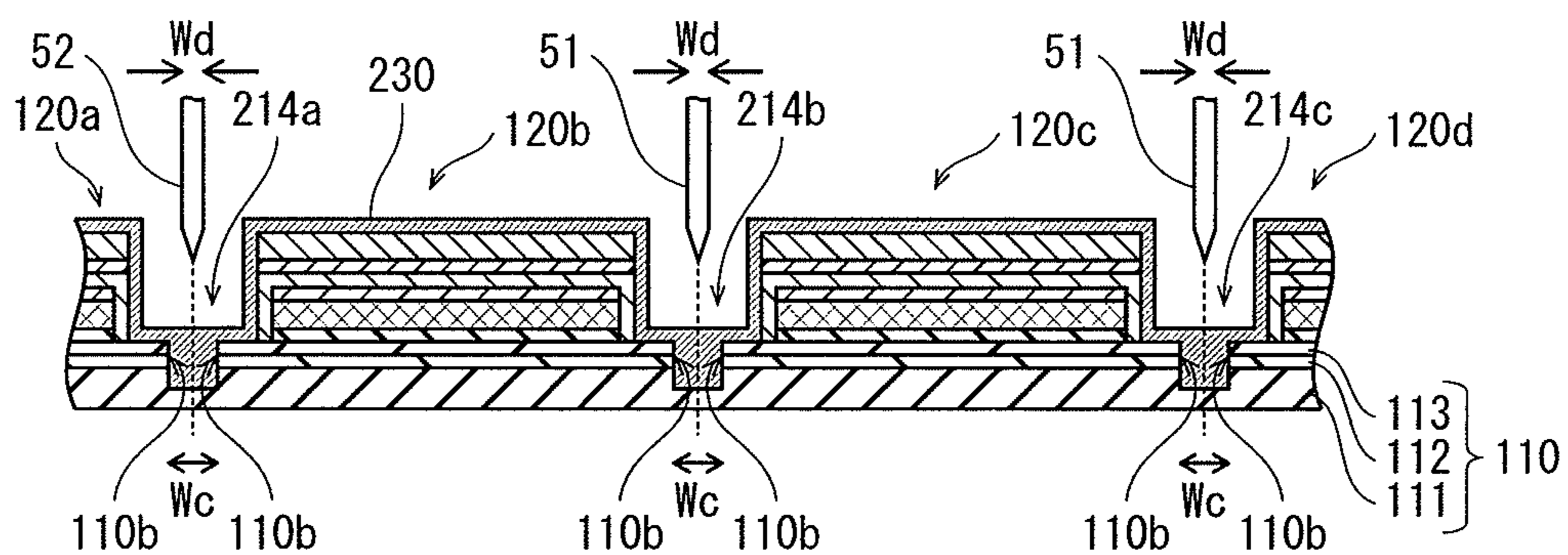


FIG. 5D

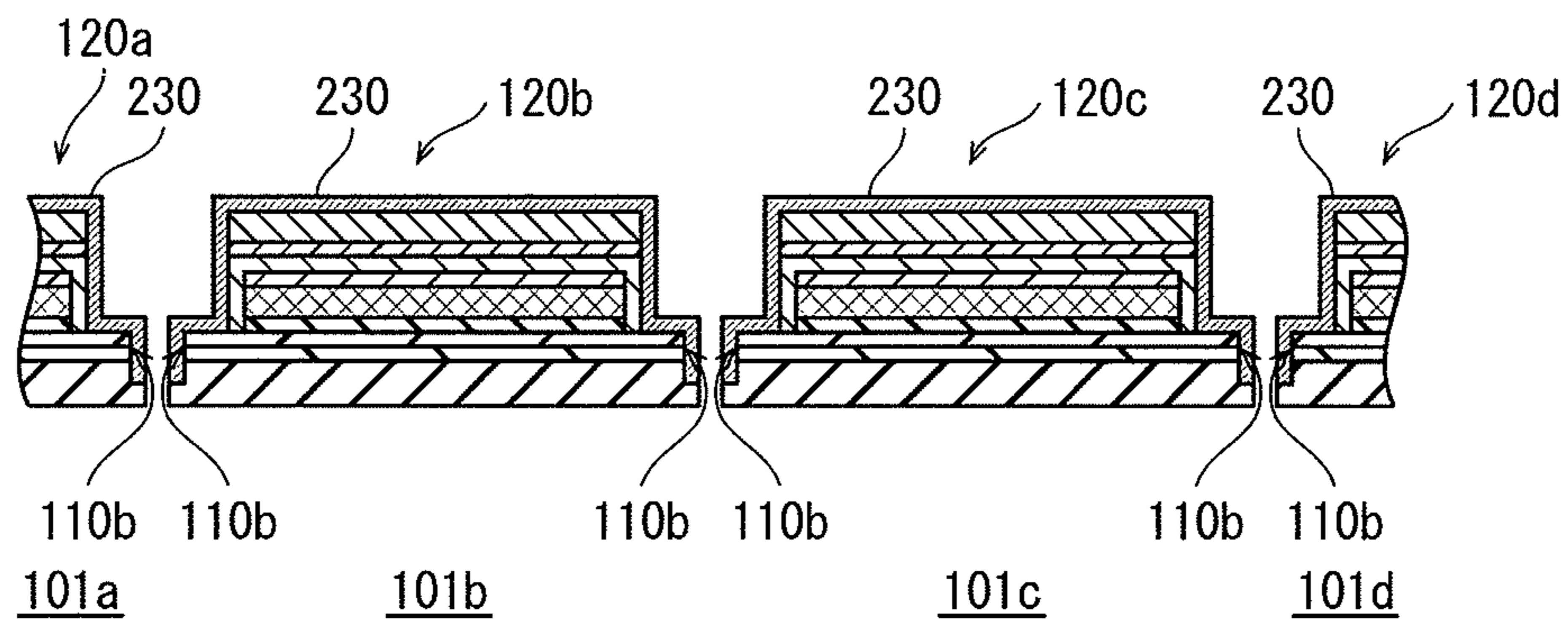


FIG. 6A

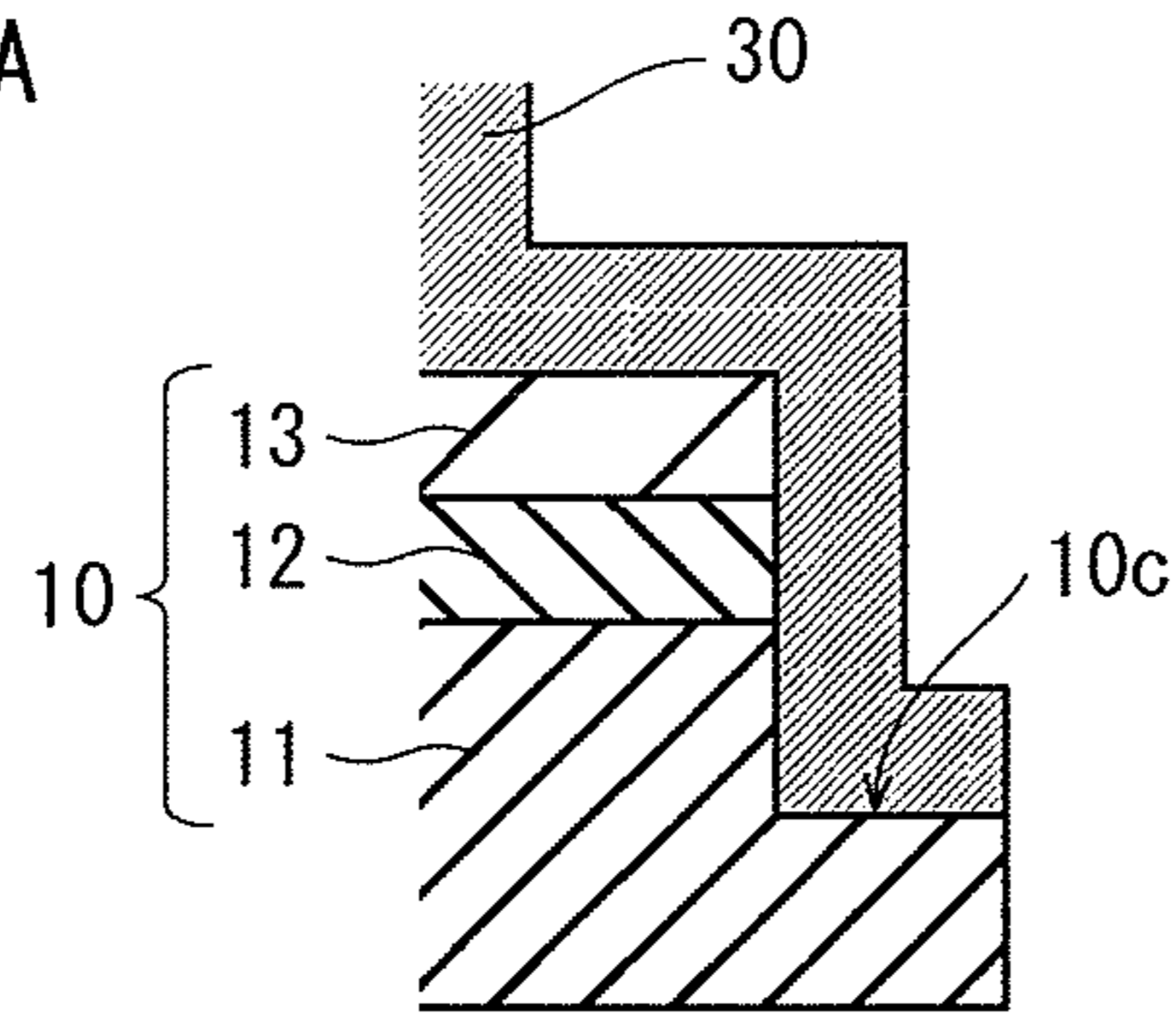


FIG. 6B

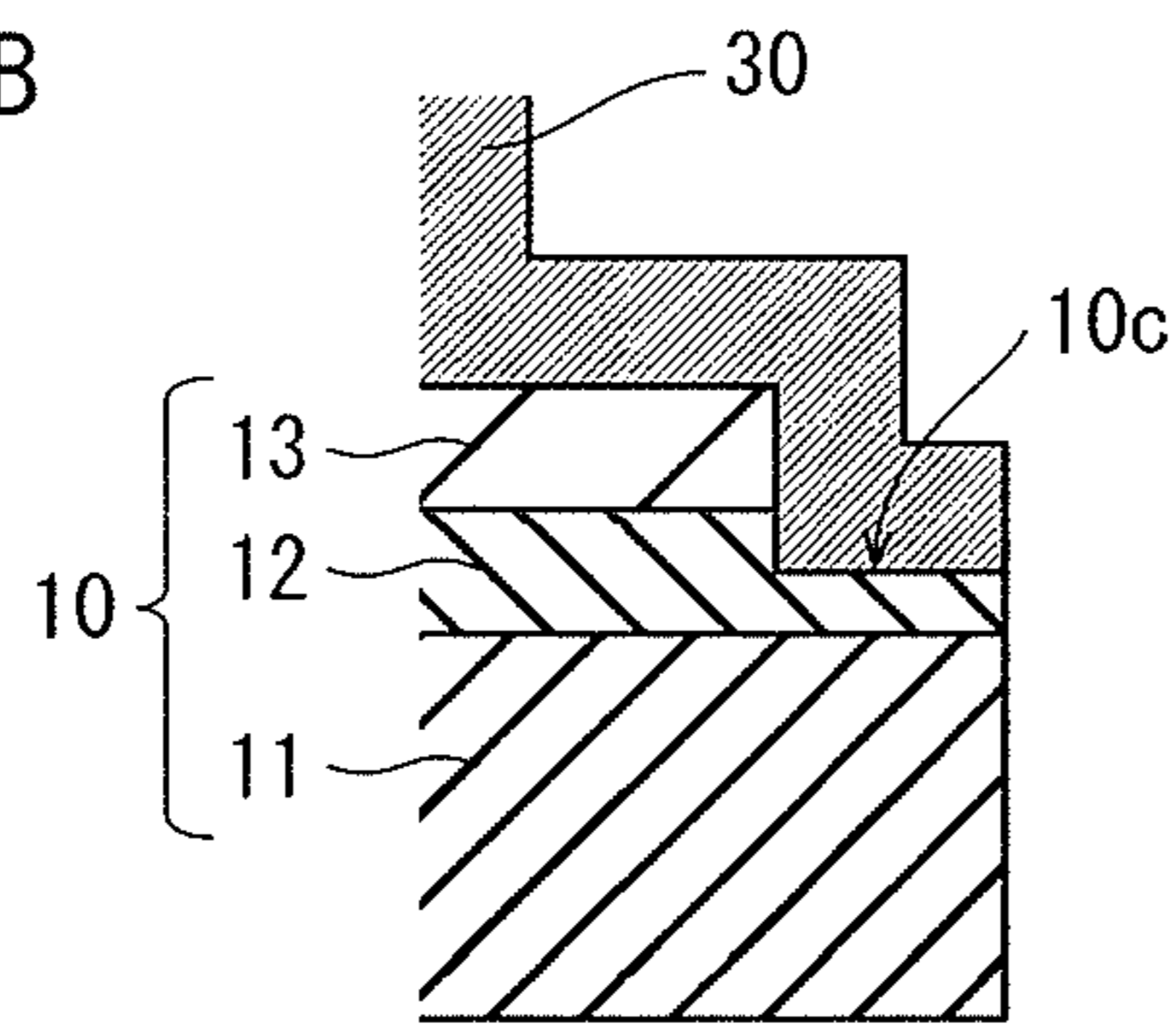


FIG. 6C

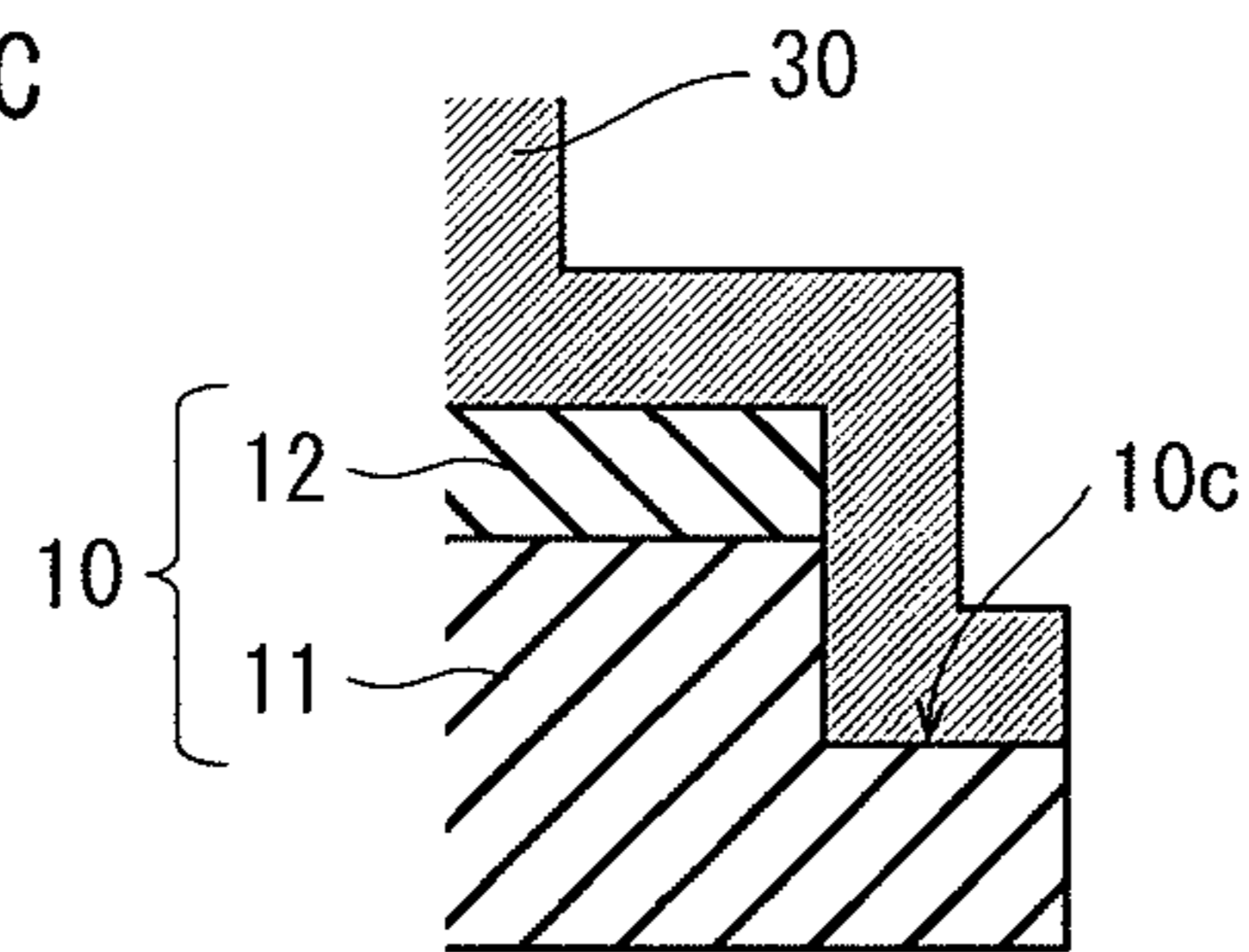


FIG. 6D

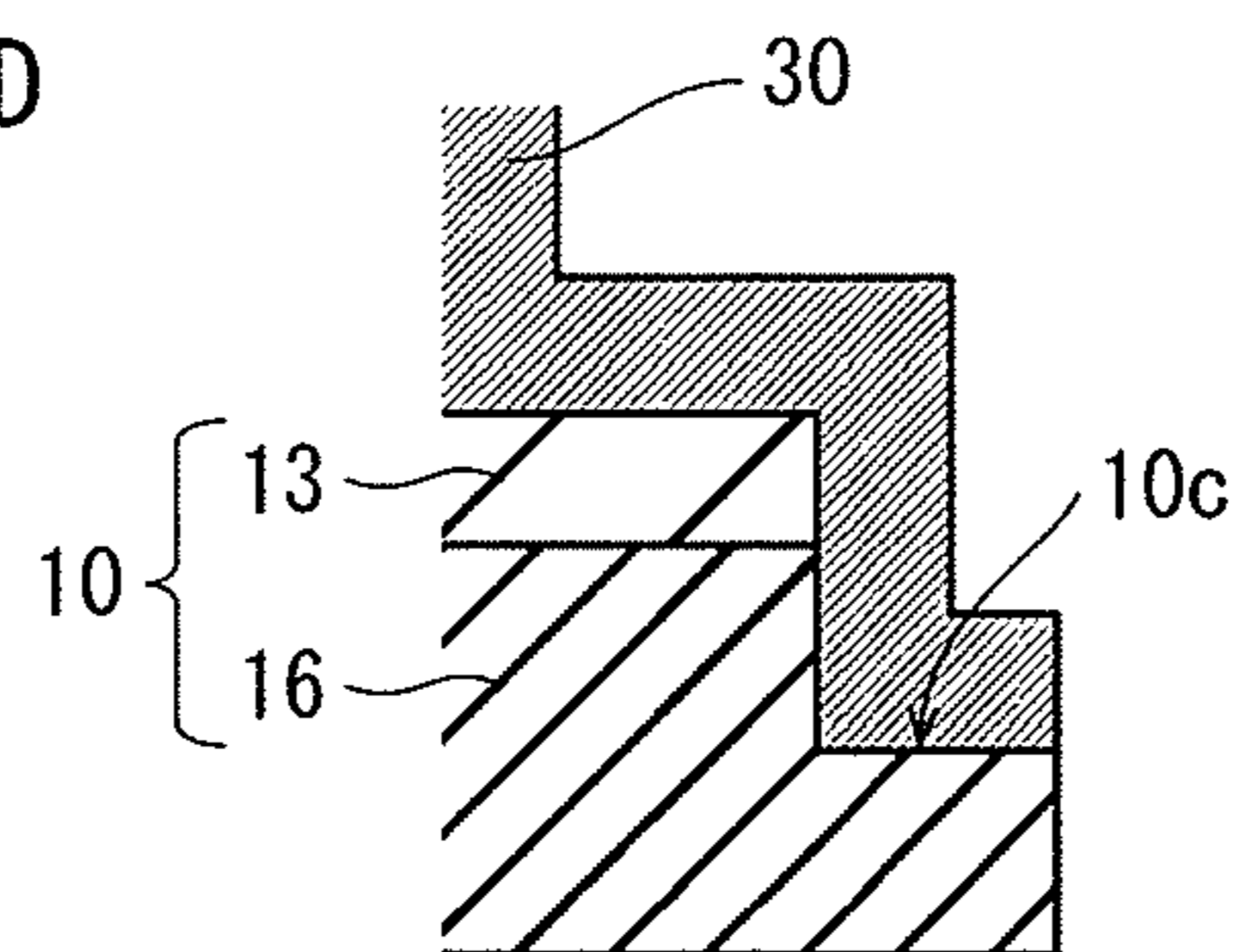




FIG. 7A

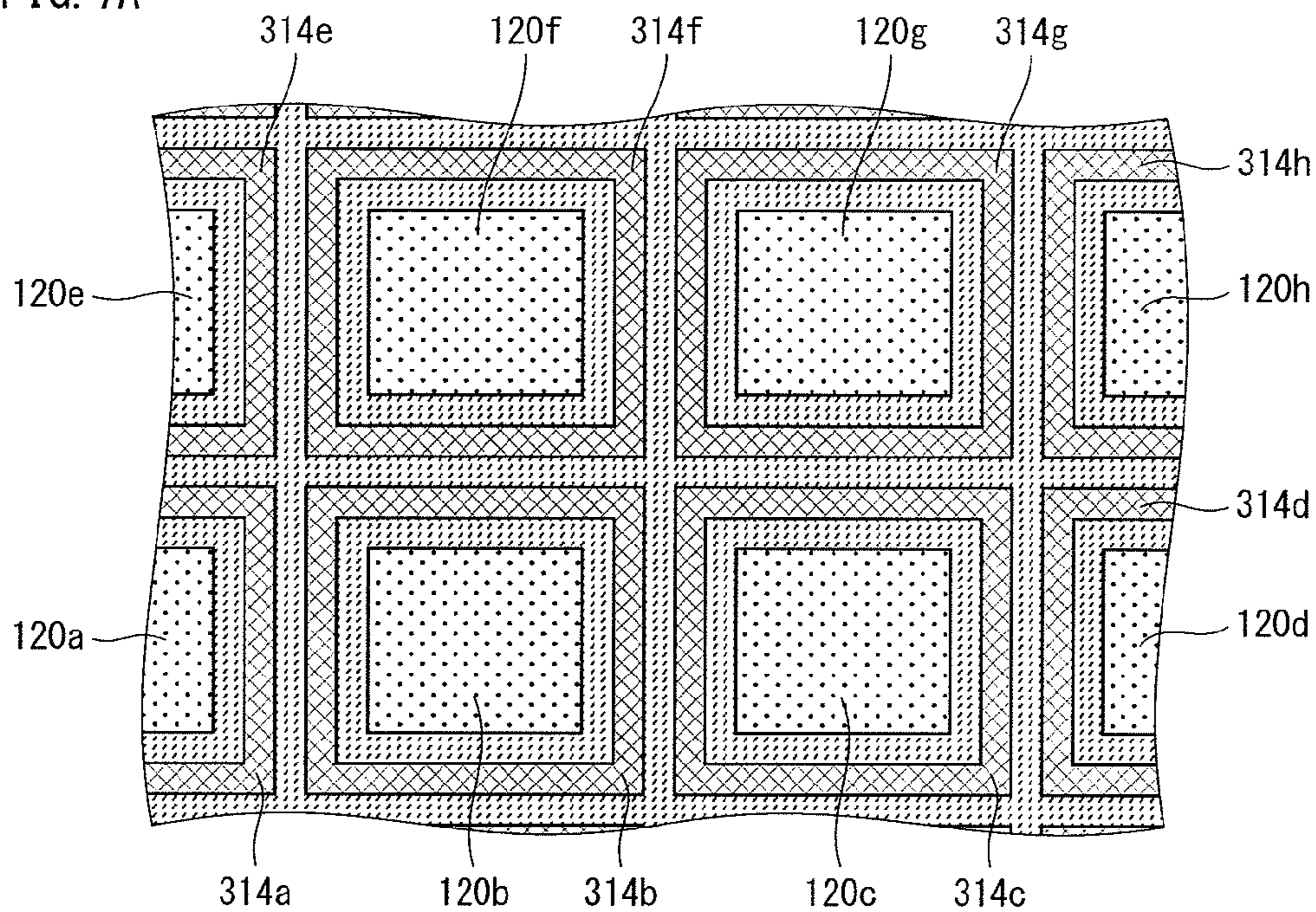
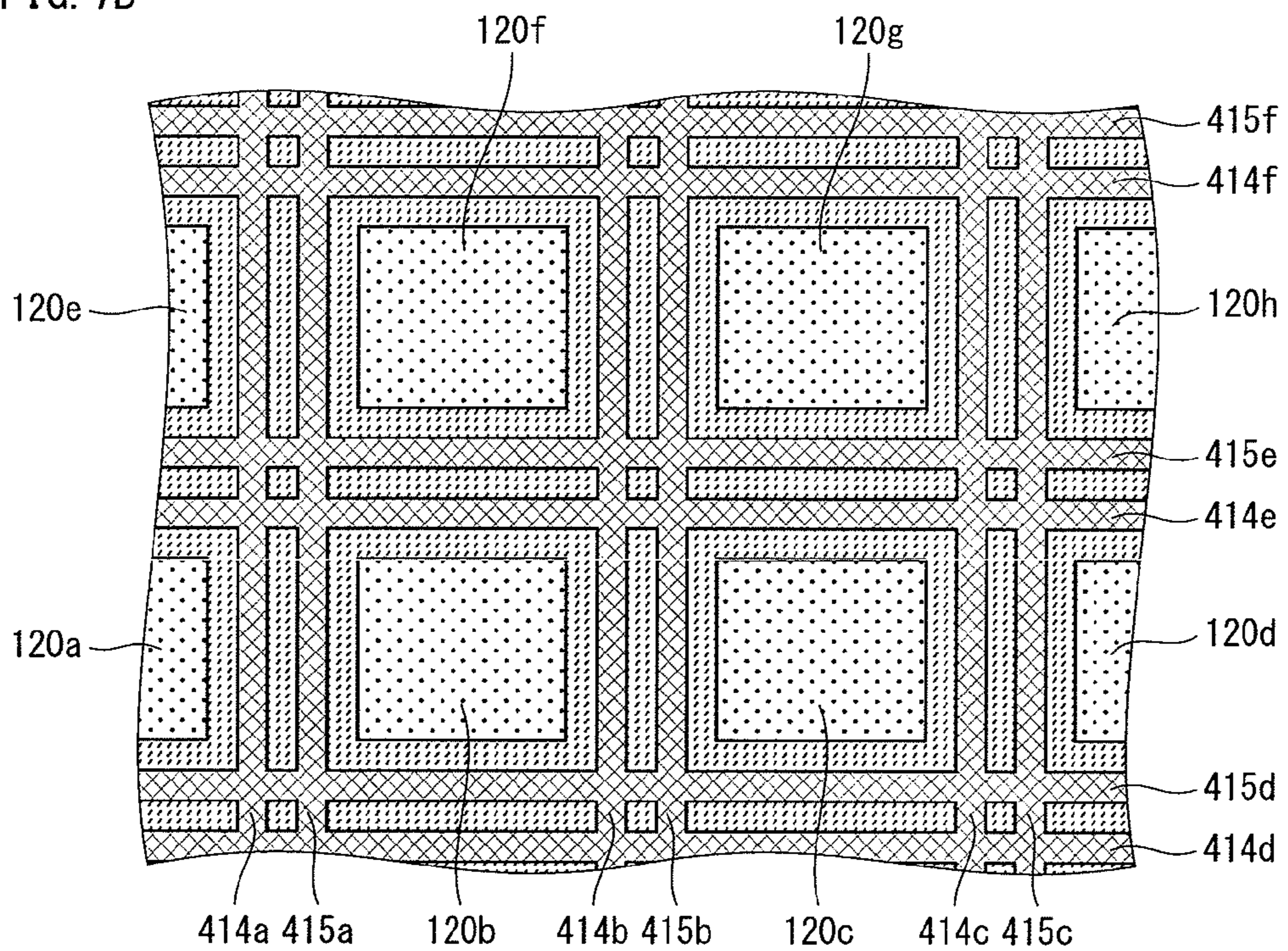


FIG. 7B





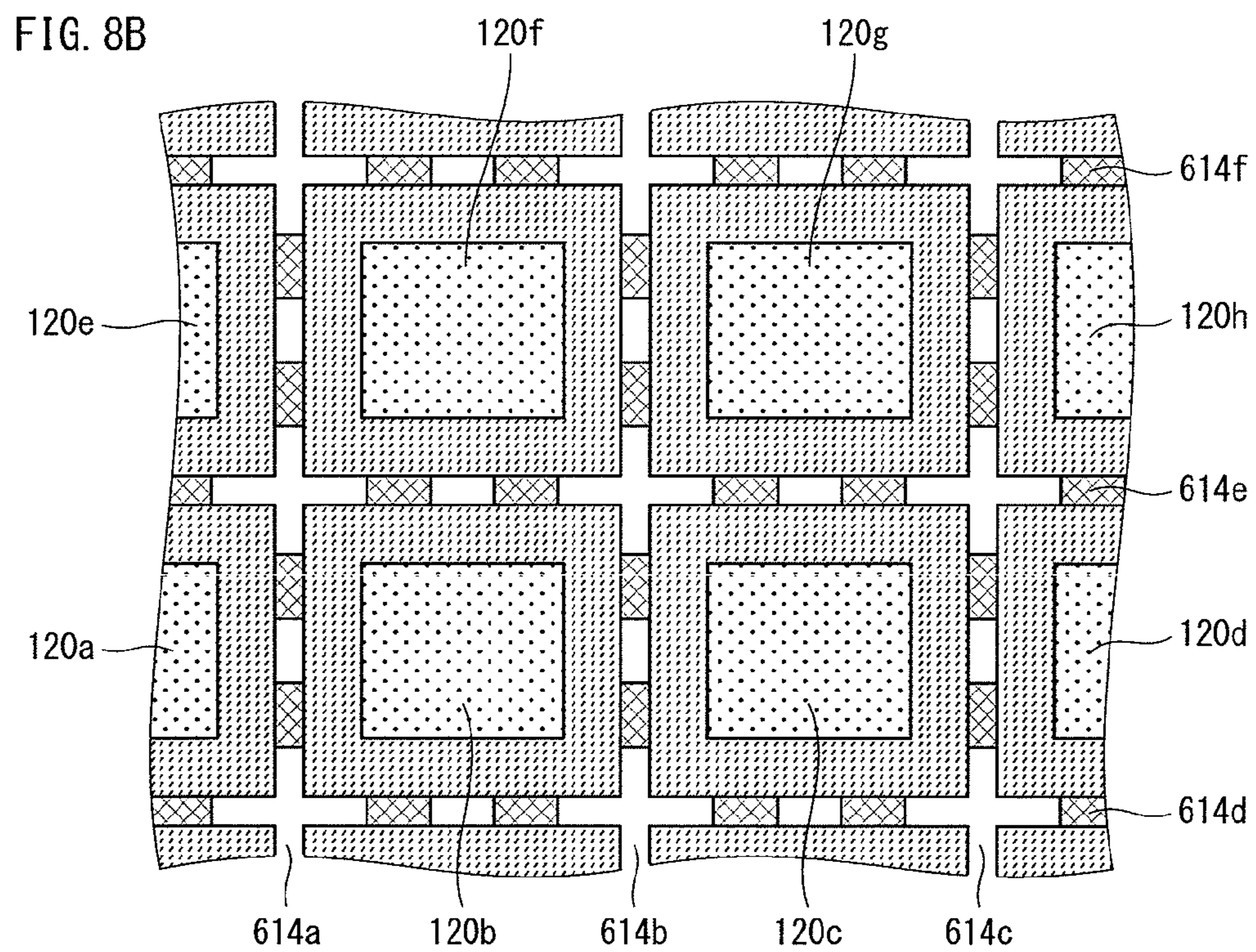
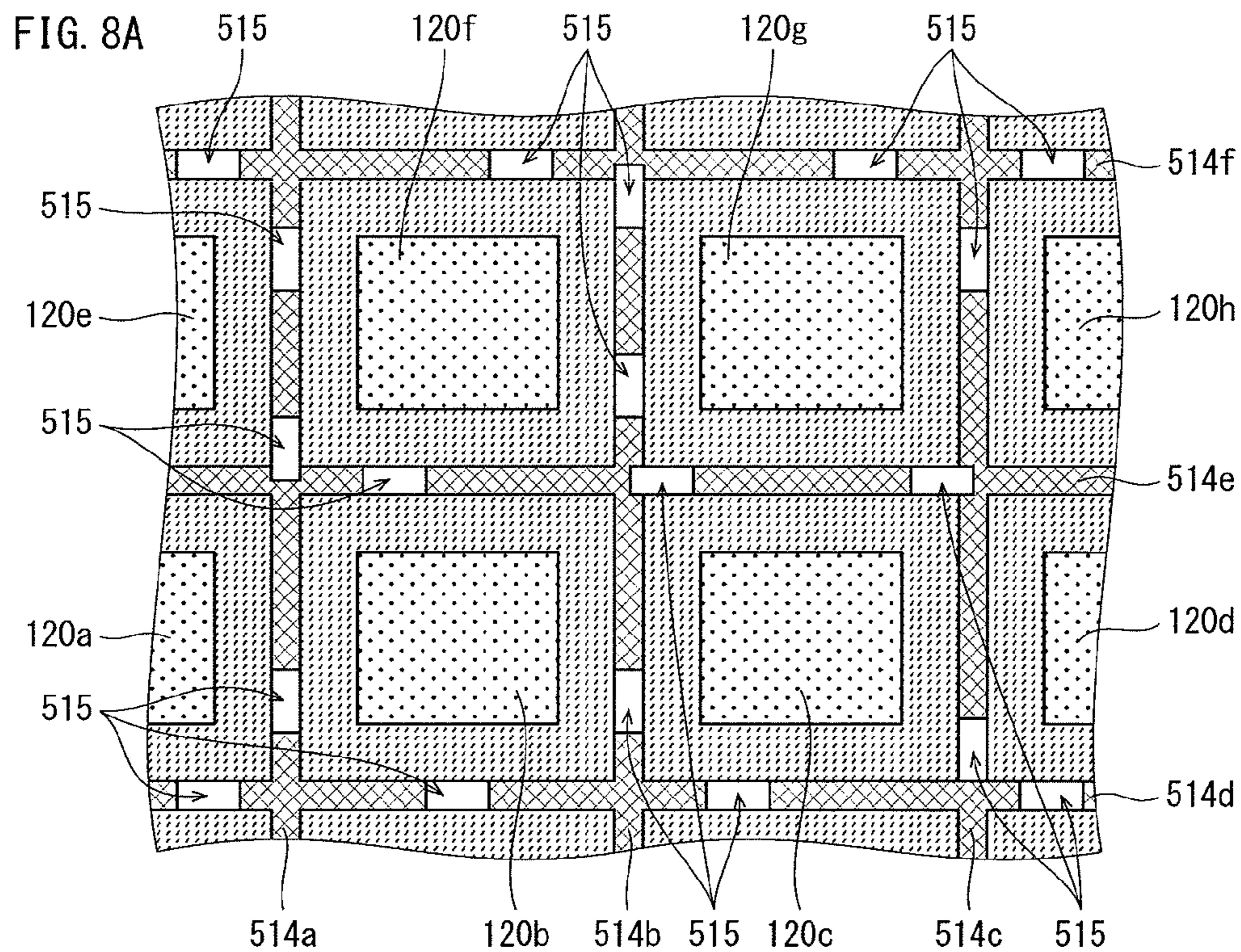


FIG. 9A

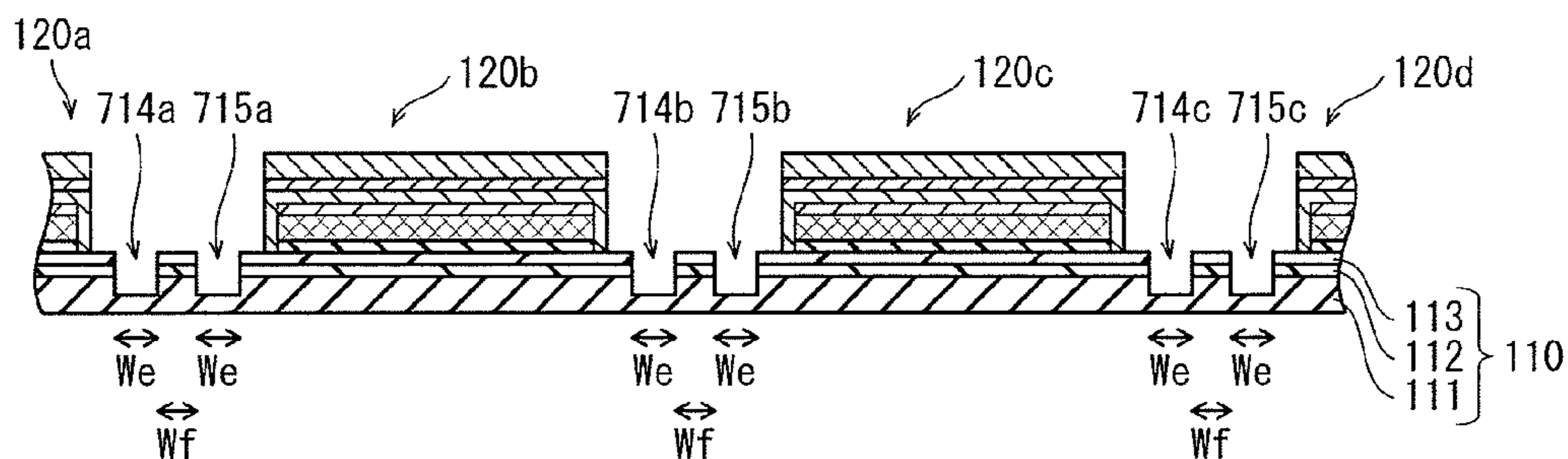


FIG. 9B

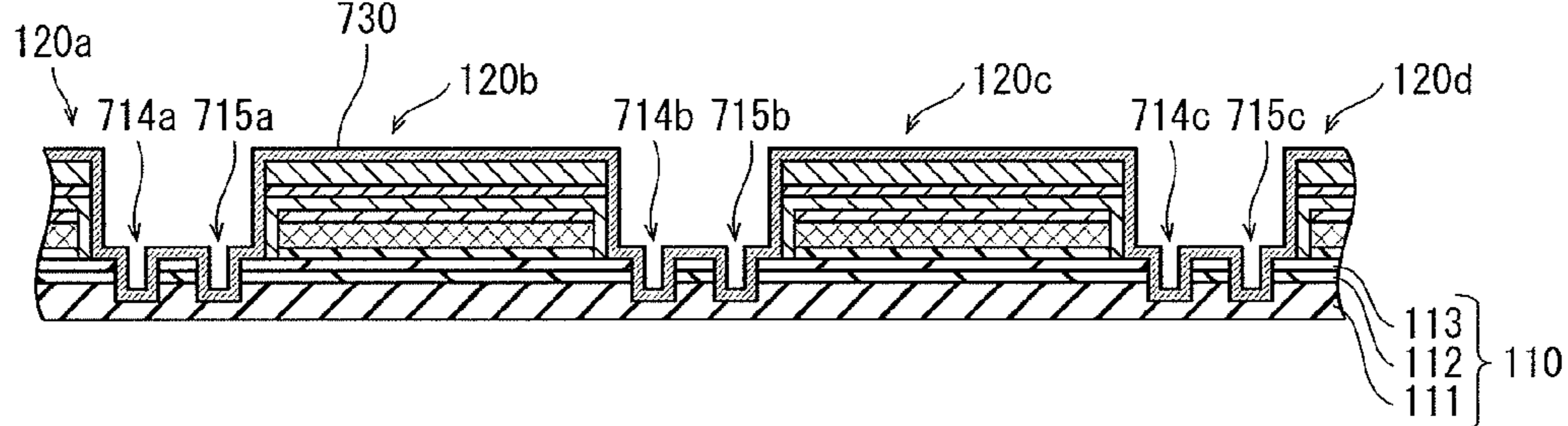


FIG. 9C

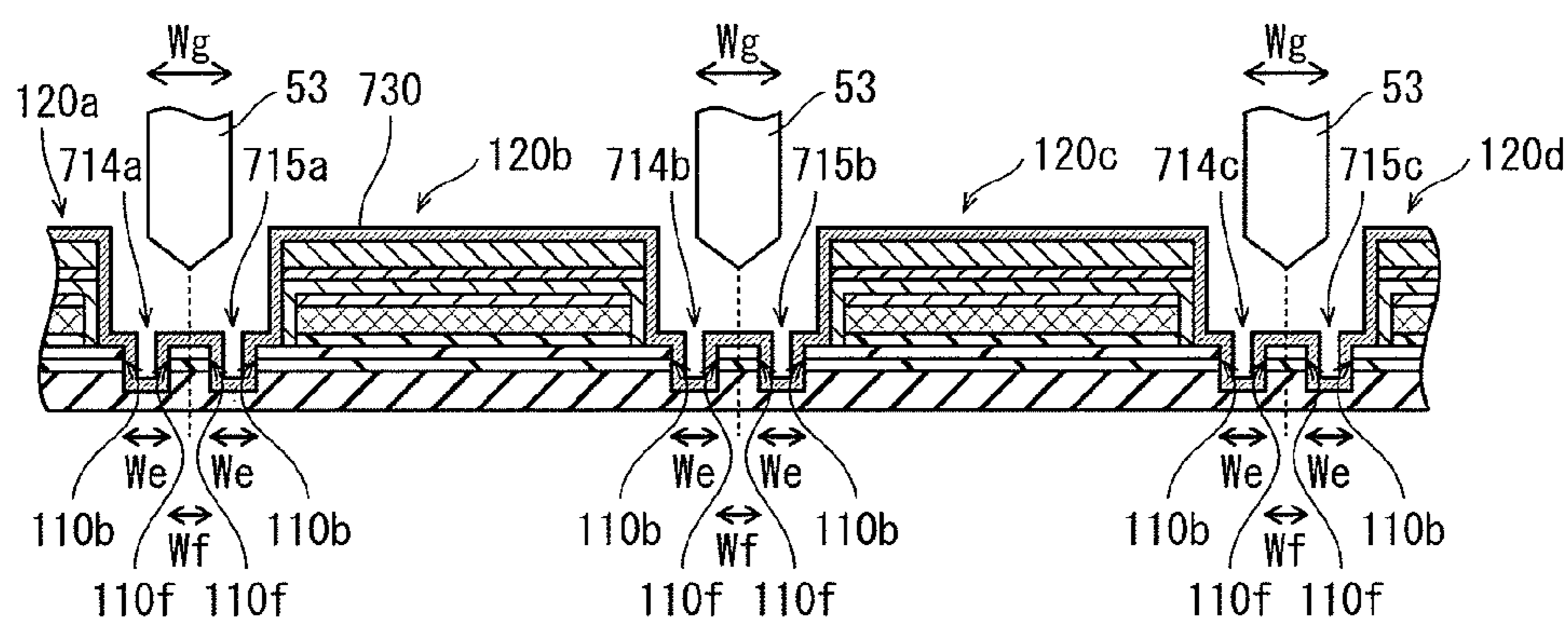


FIG. 9D

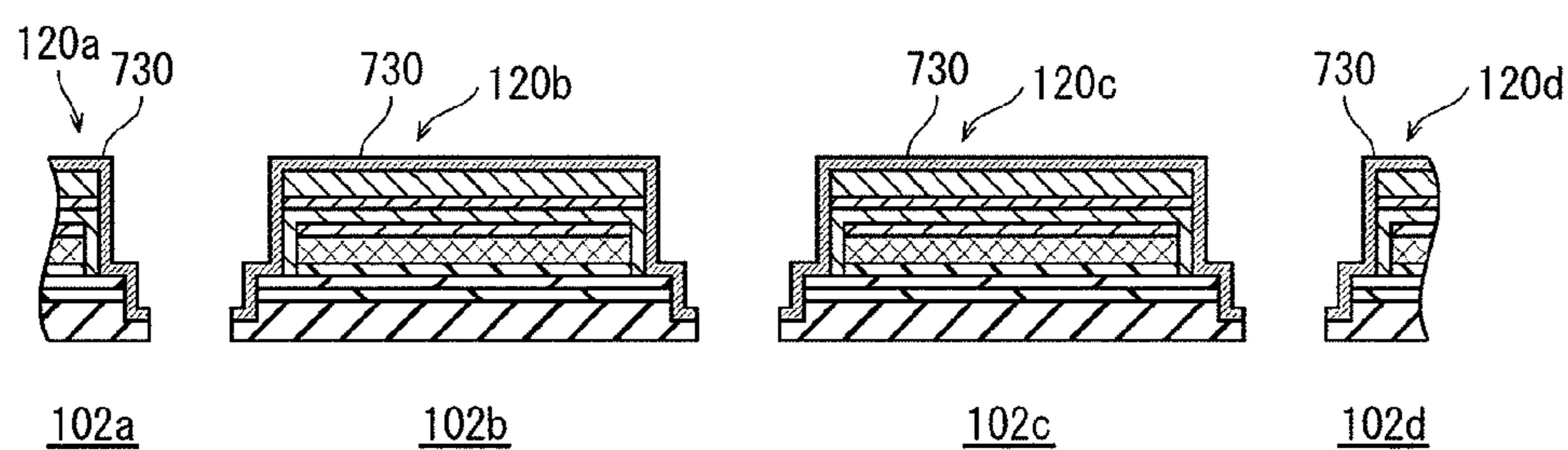




FIG. 10A

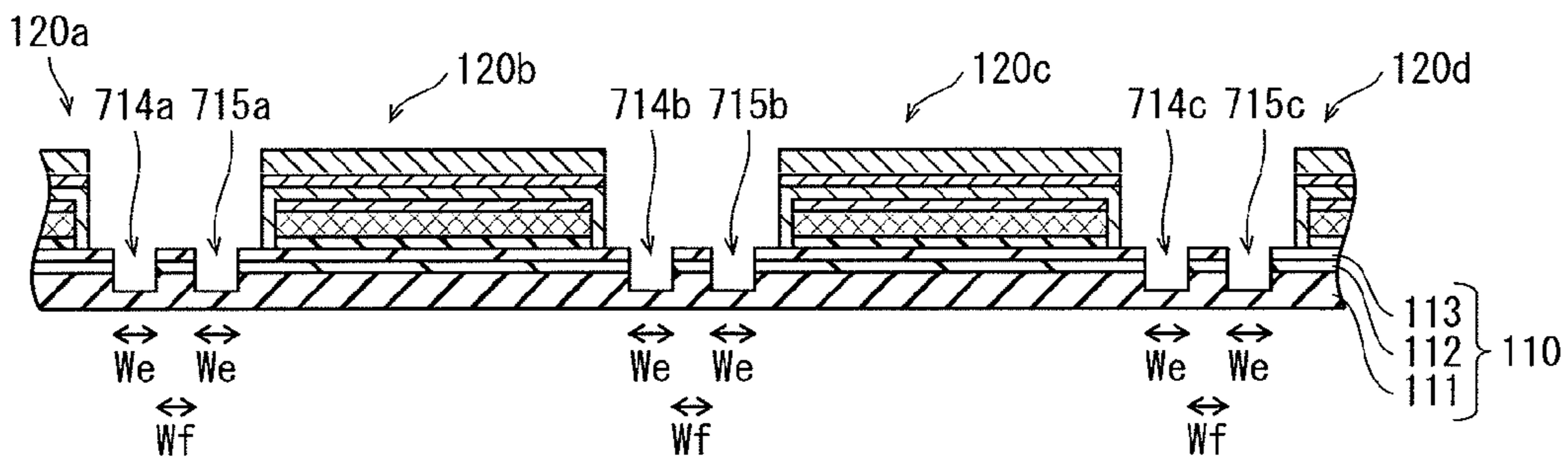


FIG. 10B

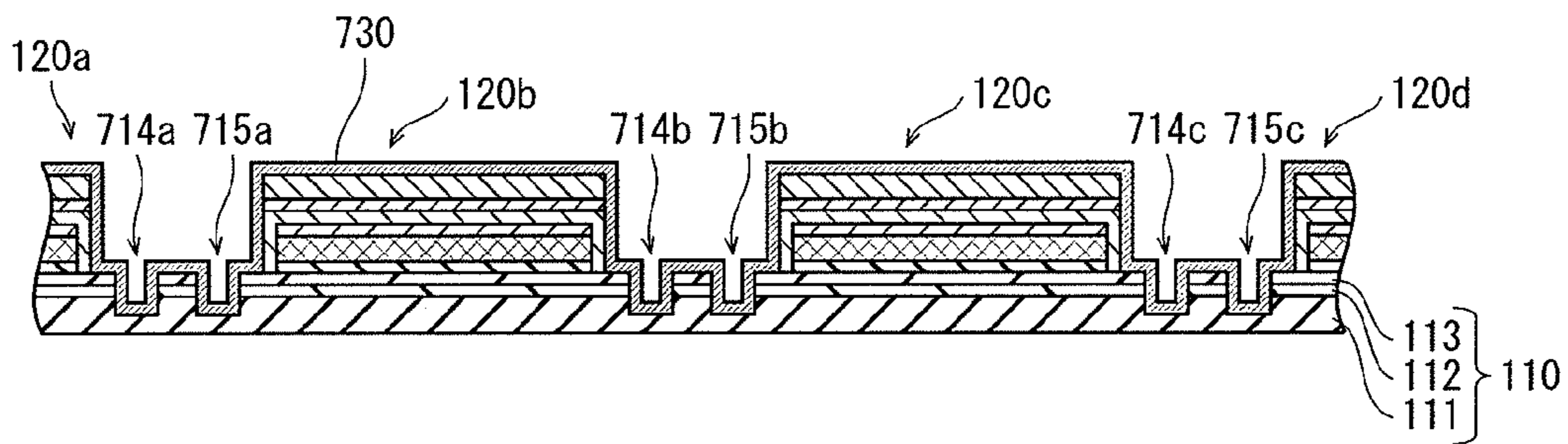


FIG. 10C

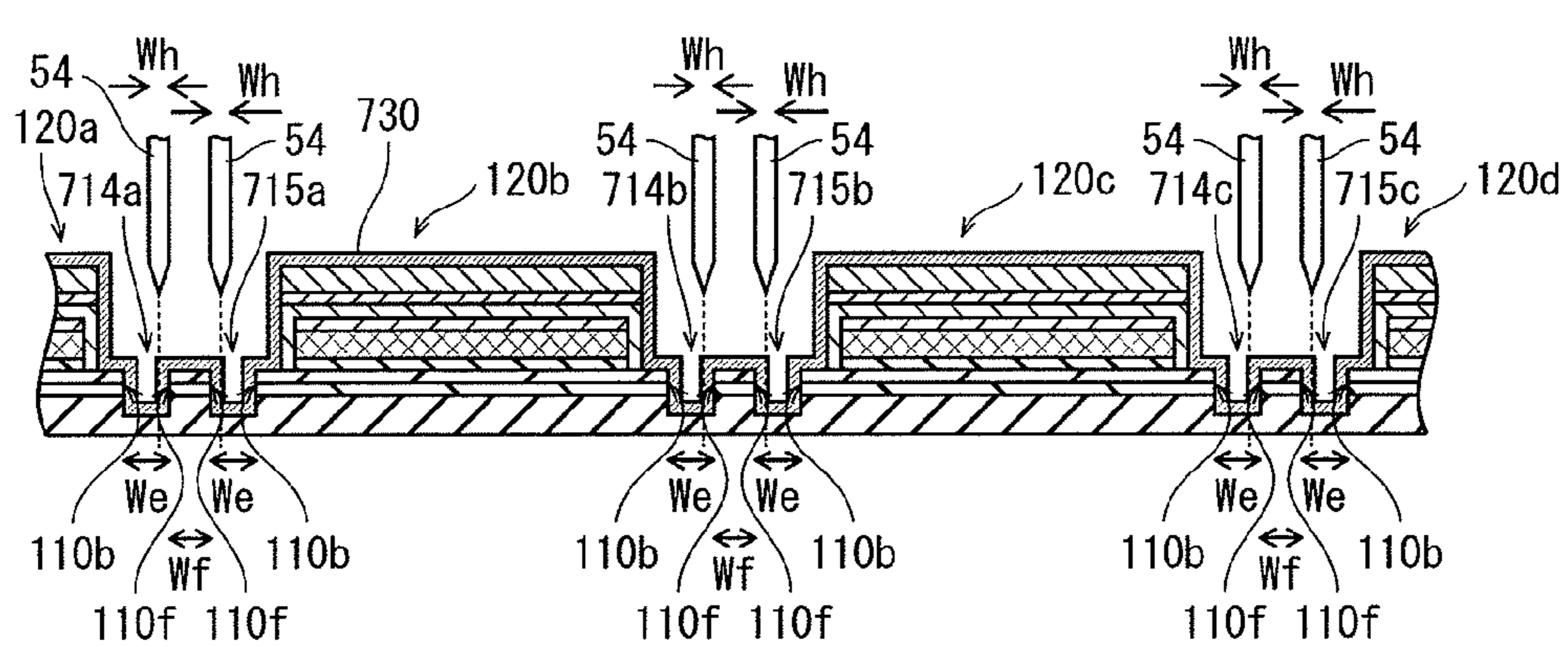


FIG. 10D

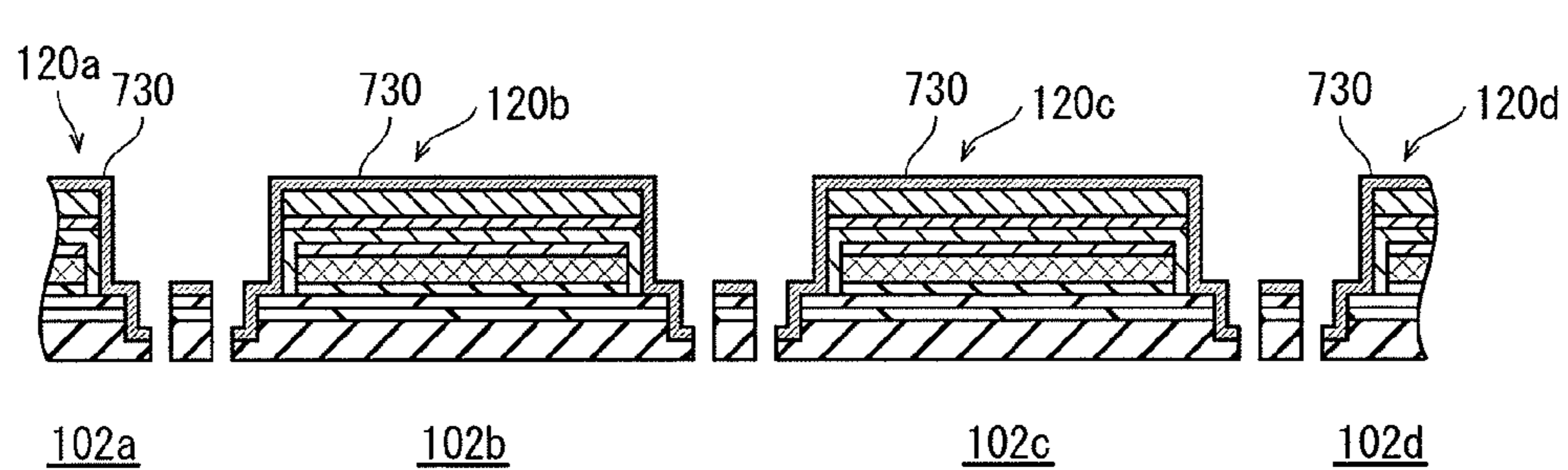


FIG. 11A

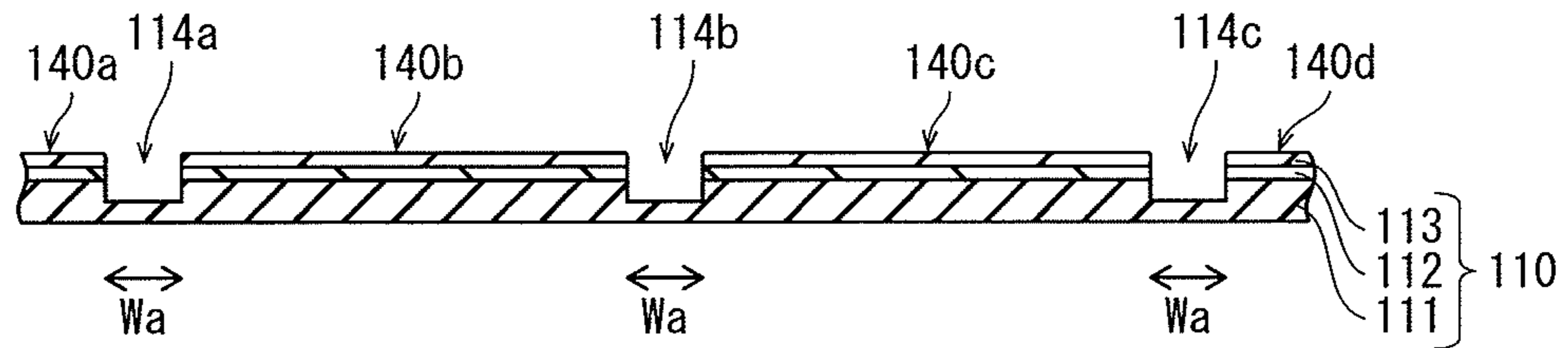


FIG. 11B

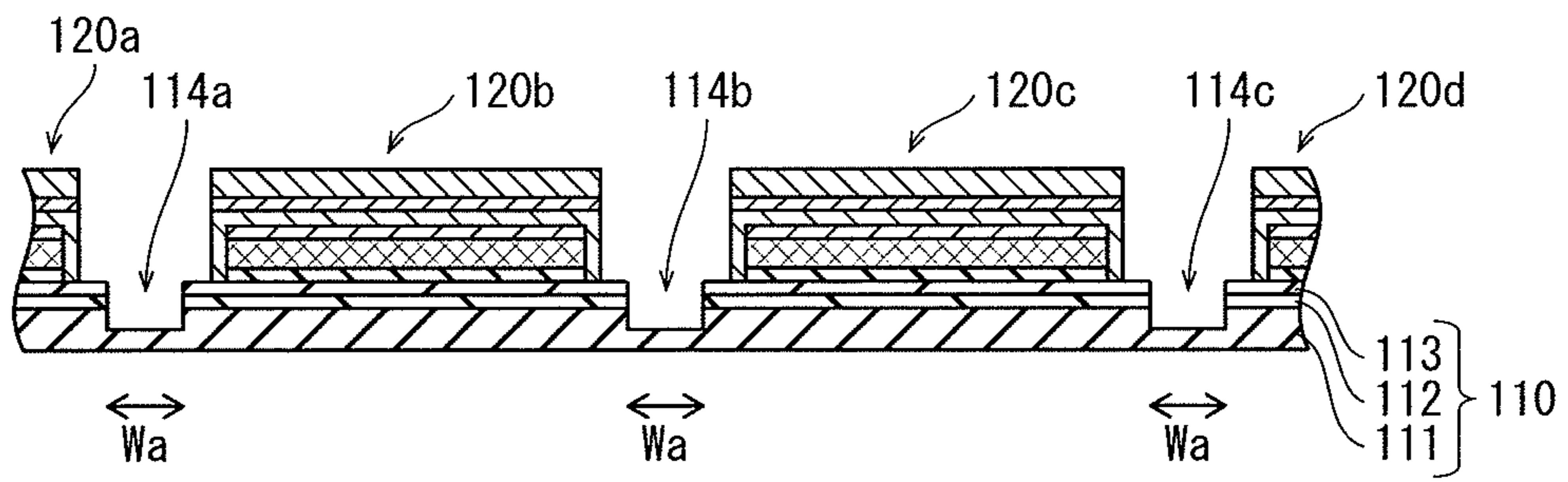
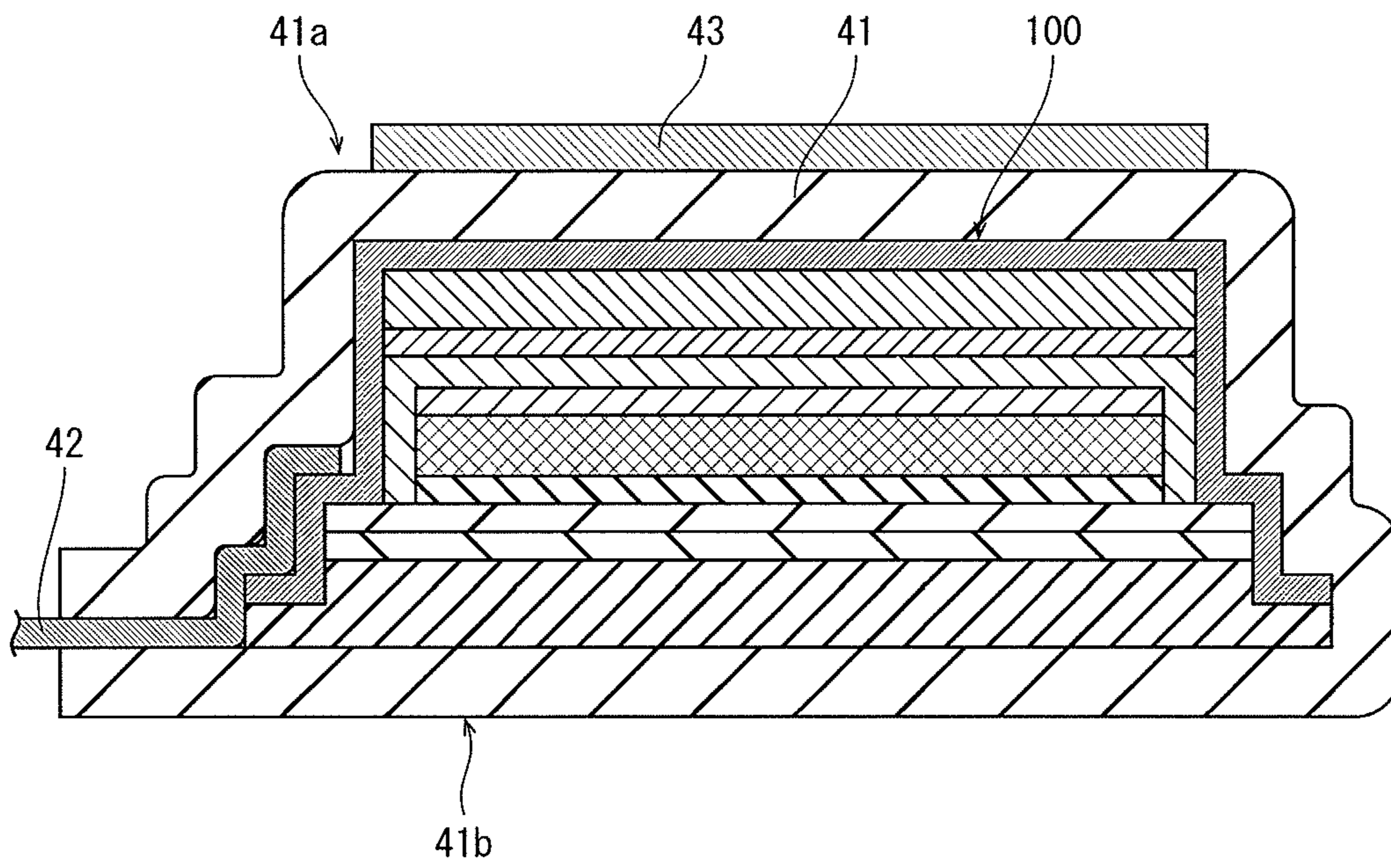


FIG. 12





## 1

**METHOD FOR MANUFACTURING LIGHT  
EMITTING DEVICE, AND LIGHT EMITTING  
DEVICE**

**Matter enclosed in heavy brackets [ ] appears in the original patent but forms no part of this reissue specification; matter printed in italics indicates the additions made by reissue; a claim printed with strikethrough indicates that the claim was canceled, disclaimed, or held invalid by a prior post-patent action or proceeding.**

CROSS REFERENCE TO RELATED  
APPLICATION

This is a *continuation reissue of U.S. application Ser. No. 15/860,927, filed Jan. 3, 2018, now U.S. Reissue Pat. No. RE48,033, issued Jun. 2, 2020, which is reissue application of U.S. Pat. No. 9,231,156, issued Jan. 5, 2016, which is a continuation application of PCT Application No. PCT/JP2012/005604, filed Sep. 5, 2012, designating the United States of America, the disclosure of all of which, including the specification, drawings and claims, [is] are incorporated herein by reference in [its] their entirety.*

TECHNICAL FIELD

The present disclosure relates to a method for manufacturing a light-emitting device such as an organic EL (Electro Luminescence) device, and in particular to the improvement of a sealing technology for preventing the degradation of a light-emitting device caused by moisture and oxygen.

DESCRIPTION OF THE RELATED ART

In recent years, development has been carried out on a technology for applying organic EL devices to displays and lighting apparatuses. An organic EL device includes a substrate and a multilayered light-emitting structure. The multilayered light-emitting structure includes an anode, a light-emitting layer, and a cathode which are layered over the substrate. When voltage is applied between the anode and the cathode, electric current flows through the light-emitting layer to emit light. In general, such a multilayered light-emitting structure includes a layer formed with a material that is easily degraded by moisture and oxygen. Accordingly, in the organic EL device, it is common to use a sealing film to cover the multilayered light-emitting structure formed on the substrate in order to prevent intrusion of moisture and oxygen from external environment.

According to Patent Literature 1, a substrate protection film made of alumina is formed on a resin substrate. Then, an organic EL structure is formed on the substrate protection film, and a device protection film made of alumina is formed on the organic EL structure (paragraphs 0044-0059). Patent Literature 1 recites that formation of these protection films can prevent degradation of the organic EL structure (paragraphs 0064-0067).

According to Patent Literature 2, a plastic film is formed into a bag, and a sealing film having gas barrier properties is formed inside the bag-shaped plastic film. Then, an organic EL panel is inserted in the bag-shaped plastic film. In this state, the bag-shaped plastic film is vacuum-compressed (paragraphs 0025-0032). Patent Literature 2 recites that the above structure can prevent degradation of the organic EL panel (paragraph 0038).

## 2

CITATION LIST

Patent Literature

Patent Literature 1

Japanese Patent Application Publication No. 2003-332042

Patent Literature 2

Japanese Patent No. 3761843

SUMMARY

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Conventionally, a multiple production method is often employed in manufacturing an organic EL device or any other device including a substrate on which a multi-layered element is formed. According to the multiple production method, after a plurality of elements are simultaneously formed on a large substrate, the substrate is cut so as to separate the plurality of elements from one another. Suppose that the multiple production method is employed to manufacture an organic EL device. In this case, a plurality of multilayered light-emitting structures are formed on a large substrate. Then, a sealing film is formed to entirely cover the multilayered light-emitting structures. The substrate over which the sealing film is formed is then cut so as to separate the multilayered light-emitting structures from one another. With the multiple production method, the multilayered light-emitting structures are formed with use of the large substrate which is easily handled during the manufacturing of the organic EL device. This improves the productivity of organic EL devices.

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On the other hand, if the substrate is cut without any measures being taken, the interface between the substrate and the sealing film will be exposed at a cut surface of the substrate. As a result, moisture and oxygen can easily infiltrate from the interface. In particular, during cutting of the substrate, stress is applied to the substrate and the sealing film. As a result, the sealing film is likely to peel off at the interface between the substrate and the sealing film, creating an infiltration path of moisture and oxygen. On the other hand, it is possible to form the sealing film after cutting the substrate into multiple substrates. In this way, the cutting surface of each separate substrate obtained as a result of the cutting is covered with the sealing film. However, this method causes the lowering of productivity since the substrates obtained as a result of the cutting are individually handled during the forming of the sealing film.

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In view of the above problem, one non-limiting and exemplary embodiment provides a technology for manufacturing a light-emitting device resistant to the infiltration of moisture and oxygen, without causing the lowering of productivity.

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In one general aspect, the techniques disclosed here feature a method for manufacturing a light-emitting device, comprising: forming, over a substrate, a plurality of multilayered light-emitting structures each including a first electrode, a light-emitting layer, and a second electrode; forming, in the substrate, a plurality of grooves that surround the multilayered light-emitting structures individually; forming, over the substrate, a sealing film that covers the multilayered light-emitting structures and the grooves; and separating the multilayered light-emitting structures from one another after forming the sealing film, by cutting the substrate such that, in each groove, part of the sealing film covering a given

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inner side surface of the groove remains, the given inner side surface being adjacent to any of the multilayered light-emitting structures.

The given inner side surface of each groove serves as part of the outer side surface of each separate substrate obtained as a result of the cutting. In the above method for manufacturing a light-emitting device, the substrate is cut into multiple substrates such that, in each groove, part of the sealing film covering the given inner side surface of the groove remains. As a result, part of the outer side surface of each separate substrate is covered by the sealing film. This prevents the exposure of the interface between the sealing film and the top surface of each separate substrate obtained as a result of the cutting, allowing for the manufacture of a light-emitting device resistant to the infiltration of moisture and oxygen. Also, according to the above method for manufacturing a light-emitting device, the sealing film is formed before the substrate is cut. Therefore, productivity is not lowered during forming of the sealing film. This allows for manufacturing of a light-emitting device resistant to the infiltration of moisture and oxygen, without causing the lowering of productivity.

These general and specific aspects may be implemented using a device.

Additional benefits and advantages of the disclosed embodiments will be apparent from the specification and figures. The benefits and/or advantages may be individually provided by the various embodiments and features of the specification and drawings disclosed, and need not all be provided in order to obtain one or more of the same.

#### BRIEF DESCRIPTION OF DRAWINGS

FIGS. 1A to 1C are cross-sectional views each showing the structure of a light-emitting device according to an embodiment of the present disclosure, where FIG. 1A is an overall view, FIG. 1B is a magnified view of a portion A, and FIG. 1C is a magnified view of a portion B.

FIGS. 2A and 2B are cross-sectional views illustrating a manufacturing process of the light-emitting device according to the embodiment of the present disclosure.

FIG. 3 is a plan view illustrating the manufacturing process of the light-emitting device according to the embodiment of the present disclosure.

FIGS. 4A to 4C are cross-sectional views illustrating the manufacturing process of the light-emitting device according to the embodiment of the present disclosure.

FIGS. 5A to 5D illustrate a modification pertaining to the formation of a sealing film in grooves.

FIGS. 6A to 6D illustrate modifications pertaining to a region covered by the sealing film.

FIGS. 7A and 7B illustrate modifications pertaining to the layout of the grooves.

FIGS. 8A and 8B illustrate modifications pertaining to the depth of the grooves.

FIGS. 9A to 9D illustrate a modification pertaining to a cutting position.

FIGS. 10A to 10D illustrate a modification pertaining to a cutting position.

FIGS. 11A and 11B illustrate modifications pertaining to the formation of the grooves.

FIG. 12 illustrates an additional sealing structure.

#### DETAILED DESCRIPTION

[Outline of an Aspect of the Present Disclosure]

One aspect of the present disclosure is a method for manufacturing a light-emitting device, comprising: forming, over a substrate, a plurality of multilayered light-emitting structures each including a first electrode, a light-emitting

layer, and a second electrode; forming, in the substrate, a plurality of grooves that surround the multilayered light-emitting structures individually; forming, over the substrate, a sealing film that covers the multilayered light-emitting structures and the grooves; and separating the multilayered light-emitting structures from one another after foaming the sealing film, by cutting the substrate such that, in each groove, part of the sealing film covering a given inner side surface of the groove remains, the given inner side surface being adjacent to any of the multilayered light-emitting structures.

The given inner side surface of each groove serves as part of the outer side surface of each separate substrate obtained as a result of the cutting. In the above method for manufacturing a light-emitting device, the substrate is cut into multiple substrates such that, in each groove, part of the sealing film covering the given inner side surface of the groove remains. As a result, part of the outer side surface of each separate substrate obtained as a result of the cutting is covered by the sealing film. This prevents the exposure of the interface between the sealing film and the top surface of each separate substrate obtained as a result of the cutting, allowing for the manufacture of a light-emitting device resistant to the infiltration of moisture and oxygen. Also, according to the above method for manufacturing a light-emitting device, the sealing film is formed before the substrate is cut. Therefore, productivity is not lowered during forming of the sealing film. This allows for manufacturing of a light-emitting device resistant to the infiltration of moisture and oxygen, without causing the lowering of productivity.

When separating the multilayered light-emitting structures, the substrate may be cut along each groove at a position closer to a center of the groove in a width direction thereof than to the given inner side surface of the groove, so that the part of the sealing film covering the given inner side surface remains.

Also, when separating the multilayered light-emitting structures, the substrate may be cut with a cutting width smaller than a width of each groove.

Furthermore, the substrate may include a resin film, a gas barrier layer, and an underlayer. The gas barrier layer may be formed over the resin film. The underlayer may be formed over the gas barrier layer, and the multilayered light-emitting structures may be formed over the underlayer. When forming the grooves, a depth of each groove may be adjusted such that a bottom surface of each groove reaches at least the gas barrier layer.

Also, the sealing film may be formed by atomic layer deposition.

One aspect of the present disclosure is a light-emitting device, comprising: a substrate having a top surface and an outer side surface; a multilayered light-emitting structure formed over the top surface of the substrate and including a first electrode, a light-emitting layer, and a second electrode; and a sealing film covering the multilayered light-emitting structure, wherein the substrate has an extended portion extending outwards from the outer side surface of the substrate, and the sealing film extends along the outer side surface of the substrate to cover a top surface of the extended portion.

One aspect of the present disclosure is a method for manufacturing a light-emitting device, comprising: forming, over a substrate, a plurality of multilayered light-emitting structures each including a first electrode, a light-emitting layer, and a second electrode; forming, in the substrate, a plurality of grooves that surround the multilayered light-



emitting structures individually; forming, over the substrate, a sealing film that covers the multilayered light-emitting structures and the grooves; and separating the multilayered light-emitting structures from one another after forming the sealing film, by cutting the substrate into individual substrate pieces along each groove, wherein the substrate includes a gas barrier layer that opposes the sealing film via the multilayered light-emitting structures, when forming the grooves, a depth of each groove is adjusted such that a bottom surface of the groove reaches at least the gas barrier layer, a given inner side surface of each groove, which is adjacent to any of the multilayered light-emitting structures, serves as part of an outer side surface of each individual substrate piece after the multilayered light-emitting structures are separated, and the part of the outer side surface of each individual substrate piece is covered with part of the sealing film.

One aspect of the present disclosure is a method for manufacturing a light-emitting device, comprising: preparing a substrate having a plurality of grooves that surround a plurality of regions individually; forming, in each region of the substrate, a multilayered light-emitting structure including a first electrode, a light-emitting layer, and a second electrode; forming, over the substrate, a sealing film that covers the multilayered light-emitting structures and the grooves; and separating the multilayered light-emitting structures from one another after forming the sealing film, by cutting the substrate into individual substrate pieces along each groove, wherein the substrate includes a gas barrier layer that opposes the sealing film via the multilayered light-emitting structures, a depth of each groove in the substrate has been adjusted such that a bottom surface of the groove reaches at least the gas barrier layer, a given inner side surface of each groove, which is adjacent to any of the multilayered light-emitting structures, serves as part of an outer side surface of each individual substrate piece after the multilayered light-emitting structures are separated, and the part of the outer side surface of each individual substrate piece is covered with part of the sealing film.

[Structure of Light-Emitting Device]

An embodiment of the present disclosure is described in detail with reference to the drawings.

FIGS. 1A to 1C are cross-sectional views each showing the structure of a light-emitting device according to an embodiment of the present disclosure. Specifically, FIG. 1A is an overall view, FIG. 1B is a magnified view of a portion A, and FIG. 1C is a magnified view of a portion B.

A light-emitting device **100** is a top emission type organic EL display. The light-emitting device **100** includes: a substrate **10**; a multilayered light-emitting structure **20** formed on the substrate **10**; and a sealing film **30** that seals the multilayered light-emitting structure **20**.

The substrate **10** includes a resin film **11**, a gas barrier layer **12**, and a TFT (Thin Film Transistor) layer **13**. For example, the resin film **11** is made of resin such as polyimide. The gas barrier layer **12** is formed on the resin film **11**. For example, the gas barrier layer **12** is made of a material having gas barrier properties such as silicon nitride. The TFT layer **13** is formed on the gas barrier layer **12**. The TFT layer **13** has drive circuits provided for respective pixels.

The multilayered light-emitting structure **20** includes an anode layer **21**, a light-emitting layer **22**, a cathode layer **23**, a sealing layer **24**, a resin layer **25**, and a resin film **26**. The anode layer **21** is made of a conductive light-reflective material. Examples of such a material include aluminum and aluminum alloy. The light-emitting layer **22** is provided between the anode layer **21** and the cathode layer **23**. When

voltage is applied between the anode layer **21** and the cathode layer **23**, electric current flows through the light-emitting layer **22**, whereby the light-emitting layer **22** emits light. FIG. 1B is a magnified view of the portion A, and shows three pixels. The light-emitting layer **22** at least includes an organic EL layer. The light-emitting layer **22** may further include various functional layers as necessary, such as a hole injection layer, a hole transport layer, an electron injection layer, and an electron transport layer. In the present embodiment, the light-emitting layer **22** includes hole injection layers **222a**, **222b**, and **222c**, hole transport layers **223a**, **223b**, and **223c**, organic EL layers **224a**, **224b**, and **224c**, and an electron transport layer **225**. Some or all the layers included in the light-emitting layer **22** are sectioned by banks on a pixel-by-pixel basis as necessary. In the present embodiment, the following layers are sectioned by banks **221**: the hole injection layers **222a**, **222b**, and **222c**; the hole transport layers **223a**, **223b**, and **223c**; and the organic EL layers **224a**, **224b**, and **224c**. The cathode layer **23** is made of a conductive light-transmissive material. Examples of such a material include ITO (Indium Tin Oxide) or IZO (Indium Zinc Oxide). The sealing layer **24** covers a multilayered structure consisting of the anode layer **21**, the light-emitting layer **22**, and the cathode layer **23**. The sealing layer **24** is made of a material having gas barrier properties such as silicon nitride. The resin layer **25** is formed on the sealing layer **24**, and is made of epoxy resin, for example. For example, the resin film **26** is made of resin such as polyimide, polyethylene terephthalate (PET), polyethylene naphthalate (PEN), or cycloolefin polymer (COP), and has flexibility and insulation properties.

For example, the sealing film **30** is made of a material having gas barrier properties, such as alumina ( $\text{Al}_2\text{O}_3$ ) or silicon nitride. The sealing film **30** covers the multilayered light-emitting structure **20**, and extends to the outer side surface of the substrate **10** to cover part of the outer side surface. FIG. 1C is a magnified view of the portion B. The substrate **10** has an extended portion **10e**, which extends outwards from the outer side surface of the substrate **10** and surrounds the entire periphery of the substrate **10**. The sealing film **30** extends from a top surface **10a** of the substrate **10** along an outer side surface **10b** to a top surface **10c** of the extended portion **10e**. Note that an outer side surface **10d** of the extended portion **10e** is not covered by the sealing film **30**. The above structure can lengthen the infiltration path of moisture and oxygen which continues from the outer side surface **10d** at which the interface between the substrate **10** and the sealing film **30** is exposed to the multilayered light-emitting structure **20**. As a result, sealing properties are improved. Also, suppose that the multiple production method is employed to manufacture the light-emitting device **100**. In this case, during cutting of the substrate, mechanical or thermal stress is applied to a cut surface of the substrate. As a result, peeling of the sealing film **30** may progress for a certain distance from the cut surface. In the present embodiment, the distance from the cut surface to the multilayered light-emitting structure **20** is lengthened. As a result, peeling of the sealing film **30** does not easily progress to the multilayered light-emitting structure **20**.

[Method for Manufacturing Light-Emitting Device]

The following describes a method for manufacturing a light-emitting device with reference to FIGS. 2A-2B, FIG. 3, and FIGS. 4A-4C. This method employs the aforementioned multiple production method.

First, a large substrate **110** is prepared, and multilayered light-emitting structures **120a**, **120b**, **120c**, **120d**, . . . are



formed on the substrate **110** (FIG. 2A). The substrate **110** includes a resin film **111**, a gas barrier layer **112**, and a TFT layer **113**. Needless to say, the substrate **110** is large enough for the formation of the multilayered light-emitting structures. Each of the multilayered light-emitting structures includes an anode layer **121**, a light-emitting layer **122**, a cathode layer **123**, a sealing layer **124**, a resin layer **125**, and a resin film **126**. Each of these layers can be formed with use of a well-known technique.

Next, on the substrate **110**, grooves **114a**, **114b**, **114c**, **114d**, **114e**, **114f**, . . . are formed to individually surround the multilayered light-emitting structures **120a**, **120b**, **120c**, **120d**, . . . (FIG. 2B and FIG. 3). FIG. 3 is a plan view showing the substrate **110** in which the grooves have been formed. As shown in FIG. 3, the multilayered light-emitting structure **120b** is surrounded by four grooves, i.e., the grooves **114a** and **114b** extending longitudinally, and the grooves **114d** and **114e** extending laterally. The multilayered light-emitting structure **120c**, located next to the multilayered light-emitting structure **120b**, is also surrounded by four grooves, i.e., the grooves **114b** and **114c** extending longitudinally, and the grooves **114d** and **114e** extending laterally. As described above, each of the multilayered light-emitting structures is surrounded by four grooves. Also, as shown in FIG. 2B, the depth of each groove is set such that the depth is substantially constant across the entirety of the groove, and that the bottom surface of the groove reaches the resin film **111** but does not pass through the substrate **110**. For example, the width of each groove is from several  $\mu\text{m}$  to several mm. For example, the grooves may be formed through a physical process such as a process using a blade or a laser. Alternatively, the grooves may be formed through a chemical process such as etching.

Next, a sealing film **130** is formed entirely over the substrate **110** (FIG. 4A). In this way, the multilayered light-emitting structures **120a**, **120b**, **120c**, **120d**, . . . and the grooves **114a**, **114b**, **114c**, **114d**, **114e**, **114f**, . . . which respectively surround the multilayered light-emitting structures **120a**, **120b**, **120c**, **120d**, . . . are covered by the sealing film **130**. For example, the thickness of the sealing film is from several nm to **100** nm. At each groove, the sealing film **130** is formed continuously from the top surface of the substrate **110**, along an inner side surface of the groove, to the bottom surface of the groove. The sealing film **130** may be formed as described above by, for example, ALD (Atomic Layer Deposition) method, CVD (Chemical Vapor Deposition) method, or an application method. In particular, the ALD method is known as a film formation method with excellent step coverage, and is thus suitable for improvement of sealing properties.

Next, cutters **51**, each having a width  $W_b$  smaller than a width  $W_a$  of each groove, are prepared (FIG. 4B). With use of the cutters **51**, the substrate **110** is cut along each groove at a position substantially at the center of the groove (FIG. 4C). As a result, the substrate **110** is cut so as to separate light-emitting devices **100a**, **100b**, **100c**, **100d**, . . . from one another. With this cutting method, parts of the sealing film **130** that cover inner side surfaces **110b** of the respective grooves remain. The inner side surfaces **110b** are adjacent to the multilayered light-emitting structures.

The inner side surfaces **110b** of the grooves formed in the substrate **110** serve as parts of the outer side surfaces of each separate substrate obtained as a result of the cutting. In the above method for manufacturing a light-emitting device, the substrate **110** is cut into multiple substrates such that, in each groove, part of the sealing film **130** covering the inner side surface **110b** of the groove remains. As a result, part of the

outer side surface of each separate substrate is covered by the sealing film **130**. This prevents the exposure of the interface between the sealing film **130** and the top surface of each separate substrate obtained as a result of the cutting, allowing for manufacturing of a light-emitting device resistant to the infiltration of moisture and oxygen.

Also, according to the above method for manufacturing a light-emitting device, the sealing film **130** is formed before the substrate **110** is cut. Therefore, productivity is not lowered during the step of forming the sealing film **130**. This allows for manufacturing of a light-emitting device resistant to the infiltration of moisture and oxygen, without causing the lowering of productivity.

Also, there may be a case where, during cutting of the substrate **110** with use of the cutters **51**, mechanical or thermal stress is applied to the cut surfaces of the substrate. As a result, peeling of the sealing film **30** may progress for a certain distance from each of the cut surfaces. However, according to the above method for manufacturing a light-emitting device, the distance from each of the cut surfaces to the corresponding multilayered light-emitting structure is lengthened. As a result, peeling of the sealing film **130** does not easily progress to the multilayered light-emitting structures.

[Modifications]

(1) Modifications Pertaining to Formation of Sealing Film in Grooves

According to the above embodiment, the sealing film is a thin film formed along the inner side surfaces and the bottom surface of each groove. However, it is not limited to such, and there may be a case where the sealing film fills each groove as shown in FIGS. 5B and 5C.

First, the multilayered light-emitting structures **120a**, **120b**, **120c**, **120d**, . . . are formed on the substrate **110**, and grooves **214a**, **214b**, **214c**, . . . are formed to individually surround the multilayered light-emitting structures **120a**, **120b**, **120c**, **120d**, . . . (FIG. 5A). Next, a sealing film **230** is formed entirely over the substrate **110** (FIG. 5B). At this time, the sealing film **230** is formed to fill inside the grooves **214a**, **214b**, **214c**, . . . This may be caused, for example, when the width of each groove is relatively small, or when the sealing film is formed by an application method. Finally, cutters **52**, each having a width  $W_d$  smaller than a width  $W_c$  of each groove, are prepared (FIG. 5C). With use of the cutters **52**, the substrate **110** is cut along each groove at a position substantially at the center of the groove (FIG. 5D). As a result, the substrate **110** is cut so as to separate the light-emitting devices **101a**, **101b**, **101c**, **101d**, . . . from one another. In this way, even when the sealing film **230** fills the grooves, the substrate **110** is cut into multiple substrates such that, in each groove, part of the sealing film **230** covering an inner side surface of the groove remains, the inner side surface being adjacent to any of the multilayered light-emitting structures.

(2) Modification Pertaining to Region Covered by Sealing Film

According to the above embodiment, as shown in FIG. 6A, the sealing film **30** covers the entirety of a side surface of the gas barrier layer **12**. However, it is not limited to such as long as the sealing film **30** reaches a layer having gas barrier properties. For example, as shown in FIG. 6B, the top surface **10c** of the extended portion is positioned at the gas barrier layer **12**, and the sealing film **30** reaches the gas barrier layer **12**. Even in such a case, the sealing film **30** is in close contact with the gas barrier layer **12**, thus improving sealing properties.



Also, in a case where the light-emitting device is a lighting device or a passive-matrix display, a TFT layer is not necessary. In such a case, the structure will be as shown in FIG. 6C. Also, in a case where a glass substrate is employed instead of a resin film, a gas barrier layer is not necessary since the glass substrate itself has gas barrier properties. In such a case, the structure will be as shown in FIG. 6D. In FIG. 6D, the substrate 10 is made up of a glass substrate 16 and a TFT layer 13, and the sealing film 30 reaches the glass substrate 16. In order for the sealing film to reach a layer having gas barrier properties, it would suffice for the bottom surface of each groove to reach the layer having gas barrier properties.

### (3) Modifications Pertaining to Layout of Grooves

According to the above embodiment, one groove extending longitudinally is formed between any two adjacent multilayered light-emitting structures, and one groove extending laterally is formed between any two adjacent multilayered light-emitting structures. However, it is not limited to such as long as the grooves can surround the multilayered light-emitting structures individually. For example, as shown in FIG. 7A, annular grooves 314a, 314b, 314c, 314d, 314e, 314f, 314g, 314h, . . . may be formed such that each of the annular grooves surrounds a different one of the multilayered light-emitting structures. With this structure, the multilayered light-emitting structure 120b is surrounded by the annular groove 314b. Also, as shown in FIG. 7B, two grooves extending longitudinally may be formed between any two adjacent multilayered light-emitting structures, and two grooves extending laterally may be formed between any two adjacent multilayered light-emitting structures. According to this structure, the multilayered light-emitting structure 120b is surrounded by four grooves, i.e., grooves 415a and 414b extending longitudinally and grooves 415d and 414e extending laterally. The multilayered light-emitting structure 120c, located next to the multilayered light-emitting structure 120b, is also surrounded by four grooves, i.e., grooves 415b and 414c extending longitudinally, and the grooves 415d and 414e extending laterally.

### (4) Modifications Pertaining to Depth of Each Groove

According to the above embodiment, the depth of each groove is substantially constant over the entirety of the groove. However, it is not limited to such as long as the large substrate can be handled as a whole. For example, the depth of each groove may partially vary, and part of each groove may penetrate through the substrate. In the example of FIG. 8A, through-holes 515 are formed in grooves 514a, 514b, 514c, 514d, 514e, and 514f. This is realized by, for example, forming the grooves with a perforation cutter. Also, in the example of FIG. 8B, the proportion of through-holes is relatively large in grooves 614a, 614b, 614c, 614d, 614e, and 614f.

In this way, although part of each groove penetrates through the large substrate, the substrate is not completely cut into multiple substrates. This allows for handling of the substrate as a whole; therefore, productivity is not lowered. Also, when part of each groove penetrates through the substrate, the distance of cutting at the time of cutting the substrate is correspondingly shortened. This reduces mechanical or thermal stress applied at the cut surfaces of the substrate.

### (5) Modifications Pertaining to Cutting Position

According to the above embodiment, only one groove is formed between any two adjacent multilayered light-emitting structures. Therefore, one of the two inner side surfaces of a groove is adjacent to one multilayered light-emitting structure, and the other to another multilayered light-emitting

structure. For example, in FIG. 4B, one of the two inner side surfaces 110b of the groove 114a is adjacent to the multilayered light-emitting structure 120a, and the other is adjacent to the multilayered light-emitting structure 120b. Accordingly, in order for parts of the sealing film covering the respective inner side surfaces of the groove to remain, it is desirable to cut the substrate along the groove at a position substantially at the center of the groove. However, as shown in FIGS. 9A-9D and 10A to 10D, when two grooves are formed between the multilayered light-emitting structures, it is not necessary to cut the substrate along each groove at a position substantially at the center of the groove.

First, the multilayered light-emitting structures 120a, 120b, 120c, 120d, . . . are formed on the substrate 110, and a pair of grooves 714a and 715a, a pair of 714b and 715b, a pair of 714c and 715c, . . . are each formed between two adjacent multilayered light-emitting structures (FIG. 9A). Between any two adjacent multilayered light-emitting structures, two grooves having a width  $W_e$  are formed. The two grooves are spaced apart from each other by a width  $W_f$ . Next, a sealing film 730 is formed entirely over the substrate 110 (FIG. 9B). Then, cutters 53, each having a width  $W_g$  which satisfies  $W_f < W_g < 2W_e + W_f$ , are prepared (FIG. 9C). With use of the cutters 53, the substrate 110 is cut between every two adjacent grooves (FIG. 9D).

Alternatively, cutters 54, each having a width  $W_h$  smaller than a width  $W_e$ , are prepared (FIG. 10C). With use of the cutters 54, the substrate 110 is cut along each groove at a position away from substantially at the center of the groove.

In the examples of FIGS. 9A-9D and 10A to 10D, the inner side surface 110b of each groove is adjacent to any of the multilayered light-emitting structures. However, an inner side surface 110f of each groove is not adjacent to any of the multilayered light-emitting structures. Accordingly, although it is necessary that parts of the sealing film 730 that cover the inner side surfaces 110b remain, it is not necessary that the inner side surfaces 110f remain. In such a case, it is not necessary to cut the substrate along each groove at a position substantially at the center of the groove. Even without doing so, parts of the sealing film that cover the inner side surfaces adjacent to the multilayered light-emitting structures still remain.

### (6) Modifications Pertaining to Cross-Sectional Shape of Grooves

According to the above embodiment, the cross-sectional shape of each groove is rectangular, and the top surface of the substrate and an inner side surface of each groove form substantially a right angle. However, it is not limited to such. For example, the cross-sectional shape of each groove may be V-shaped or inverted trapezoidal, so that the inner side surfaces of each groove are inclined. This enhances the coverage of the sealing film.

### (7) Modifications Pertaining to Means of Cutting Grooves

According to the above embodiment, the grooves are cut with a cutter. However, it is not limited to such. For example, the grooves may be cut through a physical process such as a laser process, or a chemical process such as etching.

### (8) Modifications Pertaining to Timing of Forming Grooves

According to the above embodiment, the grooves are formed in the substrate after the multilayered light-emitting structures are formed on the substrate. However, it is not limited to such. The grooves may be formed in the substrate before the multilayered light-emitting structures are formed on the substrate. In this case, first, the grooves 114a, 114b, 114c, . . . are formed to individually surround regions 140a, 140b, 140c, 140d, . . . of the substrate 110 (FIG. 11A). The



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regions 140a, 140b, 140c, 140d, . . . are regions in which the multilayered light-emitting structures 120a, 120b, 120c, 120d, . . . are to be formed. Next, the multilayered light-emitting structures 120a, 120b, 120c, 120d, . . . are respectively formed in the regions 140a, 140b, 140c, 140d, . . . of the substrate 110 (FIG. 11B). Subsequent steps are the same as the above embodiment.

Alternatively, the grooves may be formed after part of each multilayered light-emitting structure is formed on the substrate. Thereafter, the remaining part of each multilayered light-emitting structure may be formed.

## (9) Additional Sealing Structure

According to the above embodiment, each multilayered light-emitting structure is sealed with the gas barrier layer 12 and the sealing film 30. However, the present disclosure may further include an additional sealing structure. For example, in the example of FIG. 12, the light-emitting device 100 is inserted inside a bag-shaped resin film 41 in which a gas barrier layer is formed. In this state, the bag-shaped resin film 41 is vacuum-compressed. The light-emitting device 100 is supplied with power via an outer lead 42. An electrode 43 for a touch panel is formed on a top surface 41a of the bag-shaped resin film 41. In a case where the light-emitting device 100 is a bottom emission type, the electrode 43 for a touch panel is formed on a bottom surface 41b of the bag-shaped film 41.

## (10) Scope of Application

According to the above embodiment, the light-emitting device is an organic EL display. However, the light-emitting device is not necessarily an organic EL display and may be another light-emitting device as long as the device needs sealing. For example, the light-emitting device may be an organic EL lighting apparatus. Note that organic EL displays come in many types. For example, depending on the method for extracting light, there are a top emission type, a bottom emission type, a double-sided emission type, etc. Also, depending on the method for driving, there are an active matrix type, a passive matrix type, etc. The present disclosure is applicable to any type of organic EL display.

[Industrial Applicability]

The present disclosure is applicable to displays and lighting apparatuses, for example.

## REFERENCE SIGNS LIST

10 substrate  
 10a top surface of substrate  
 10b outer side surface of substrate  
 10c top surface of extended portion  
 10d outer side surface  
 10e extended portion  
 11 resin film  
 12 gas barrier layer  
 13 TFT layer  
 16 glass substrate  
 20 multilayered light-emitting structure  
 21 anode layer  
 22 light-emitting layer  
 23 cathode layer  
 24 sealing layer  
 25 resin layer  
 26 resin film  
 30 sealing film  
 41 resin film  
 42 outer lead  
 43 electrode for touch panel  
 51, 52, 53, and 54 cutter

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100 light-emitting device  
 110 substrate  
 120 multilayered light-emitting structure  
 221 bank  
 222a hole injection layer  
 223a hole transport layer  
 224a organic EL layer  
 225 electron transport layer  
 100a-100d light-emitting device  
 110b inner side surface of groove  
 110b inner side surface of groove  
 111 resin film  
 112 gas barrier layer  
 113 TFT layer  
 114a-114f groove  
 120a-120h multilayered light-emitting structure  
 121 anode layer  
 122 light-emitting layer  
 123 cathode layer  
 124 sealing layer  
 125 resin layer  
 126 resin film  
 130 sealing film  
 214a-214c groove  
 314a-314f groove  
 414a-414f groove  
 415a-415f groove  
 514a-514f groove  
 515 through-hole  
 614a-614f groove  
 714a-714c groove  
 715a-715c groove

The invention claimed is:

- [1. A light-emitting device, comprising:  
 a substrate having a top surface, a bottom surface, and an outer side surface;  
 a multilayered light-emitting structure disposed over the top surface of the substrate, and including a first electrode, a light-emitting layer, and a second electrode; and  
 a sealing film covering the multilayered light-emitting structure, wherein the substrate includes a gas barrier layer that opposes the sealing film via the multilayered light-emitting structure, and  
 the outer side surface of the substrate includes a first region extending from the top surface of the substrate to the gas barrier layer, and a second region extending from the gas barrier layer to the bottom surface of the substrate, the first region being covered by the sealing film, and a part of the second region is covered by the sealing film while another part of the second region is not covered by the sealing film,  
 wherein the gas barrier material is an electrical insulator.]
- [2. The light-emitting device of claim 1, wherein the substrate further comprises:  
 a thin film transistor layer disposed above the gas barrier layer; and  
 a resin film layer disposed below the gas barrier layer.]
- [3. The light-emitting device of claim 2, wherein a portion of the resin film layer extends outwards from the outer side surface to be longer than at least one of the thin film transistor layer and the gas barrier layer in a direction of the extension.]
- [4. The light-emitting device of claim 2, wherein the first electrode and the second electrode contact the thin film transistor layer.]



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[5. The light-emitting device of claim 2, wherein the thin film transistor layer is a flat structure without protrusions or recesses.]

6. A light-emitting device, comprising:  
 a substrate having a top surface, a bottom surface, and an 5  
 outer side surface;  
 a multilayered light-emitting structure disposed over the  
 top surface of the substrate, and including a first  
 electrode, a light-emitting layer, and a second elec- 10  
 trode; and  
 a sealing film covering the multilayered light-emitting  
 structure,  
 wherein the substrate includes:  
 a gas barrier layer;  
 a thin film transistor layer disposed above the gas 15  
 barrier layer; and  
 a base layer disposed below the gas barrier layer,

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- a first part of the outer side surface of the substrate, which  
 includes the thin film transistor layer and at least a part  
 of the gas barrier layer, is covered by the sealing film,  
 and a second part of the outer side surface of the  
 substrate, which includes at least a part of the base  
 layer, is not covered by the sealing film, and  
 the gas barrier layer is an electrical insulator.  
 7. The light-emitting device according to claim 6,  
 wherein the sealing film directly contacts the part of the  
 gas barrier layer.  
 8. The light-emitting device according to claim 6,  
 wherein the base layer is made of resin.  
 9. The light-emitting device according to claim 6,  
 wherein a third part of the outer side surface of the  
 substrate, which includes another part of the base  
 layer, is covered by the sealing film.

\* \* \* \* \*